

FERROELECTRIC MEMORY DEVICE AND METHOD FOR READING DATA FROM THE SAME

BACKGROUND OF THE INVENTION

5 The present invention relates to ferroelectric memory devices using ferroelectric capacitors in memory cells thereof and to methods for reading data from the same. More specifically, the present invention relates to a ferroelectric memory device in which a reference potential is generated by two reference cells retaining different data, and to a method for reading data from the same.

10 Recently, developments of ferroelectric memory devices have been proceeding. The ferroelectric memory device uses as memory elements ferroelectric capacitors having capacitor insulating films of ferroelectric, and retains data by utilizing remnant polarization held in the ferroelectric. Heretofore, the ferroelectric memory device has generally employed as a memory cell a two-transistor, two-capacitor memory cell which retains
15 complementary data in two ferroelectric capacitors by using two transistors. Because of a recent demand for an increased data capacity and a recent trend toward a miniaturized process technology, the ferroelectric memory device has alternatively applied a one-transistor, one-capacitor memory cell.

 The one-transistor, one-capacitor memory cell is provided with one bit line pair for
20 reading data. Of the bit line pair connected to the memory cell, one bit line is supplied with a reference potential (reference level) and the other bit line is supplied with a potential according to remnant polarization. The potential difference across the two bit lines is then amplified by a sense amplifier, whereby data reading for the memory cell is performed. For example, Japanese Unexamined Patent Publication No.7-262768 discloses an
25 exemplary one-capacitor, one-transistor memory cell of this type in which a reference potential is generated by two reference cells retaining different data.

 A conventional ferroelectric memory device employing the one-transistor, one-

capacitor memory cells will be described below with reference to the accompanying drawings.

FIG. 9 shows a circuit configuration of the conventional ferroelectric memory device. Referring to FIG. 9, the conventional ferroelectric memory device includes, as
5 memory cells for retaining data, first to fourth memory cells **101** to **104** composed of transistors **T1** to **T4** and ferroelectric capacitors **C1** to **C4**, respectively.

In the transistors **T1** to **T4**, gates are each connected to either of word lines **WL1** and **WL2**, and drains are connected to bit lines **BL1** to **BL4**, respectively. In the ferroelectric capacitors **C1** to **C4**, first electrodes are connected to sources of the transistors
10 **T1** to **T4**, respectively, and second electrodes are each connected to either of cell plate lines **CP1** and **CP2**.

The conventional ferroelectric memory device further includes, as memory cells for retaining data used in the generation of a reference potential, first to fourth reference cells
15 **105** to **108** composed of transistors **T5** to **T8** and ferroelectric capacitors **C5** to **C8**, respectively.

In the transistors **T5** to **T8**, gates are each connected to either of reference word lines **RWL1** and **RWL2**, and drains are connected to the bit lines **BL1** to **BL4**, respectively. In the ferroelectric capacitors **C5** to **C8**, first electrodes are connected to sources of the transistors **T5** to **T8**, respectively, and second electrodes are each connected
20 to either of reference cell plate lines **RCP1** and **RCP2**.

The first to fourth reference cells **105** to **108** are provided with first to fourth reset circuits **109** to **112**, respectively, as circuits for writing predetermined pieces of data in the respective cells. The first to fourth reset circuits **109** to **112** are composed of transistors **T9** to **T12** whose drains are connected to the first electrodes of the ferroelectric capacitors **C5**
25 to **C8**, respectively.

The first and third bit lines **BL1** and **BL3** are connected to each other through a first switch circuit **113** composed of a transistor **T13**. The second and fourth bit lines **BL2**

and **BL4** are connected to each other through a second switch circuit **114** composed of a transistor **T14**.

The first and second bit lines **BL1** and **BL2** are both connected to a first precharge circuit **115** composed of two transistors **T15** and **T16**, and also connected to a first sense amplifier **116**. The first and second bit lines **BL1** and **BL2** serve as a bit line pair for the first sense amplifier **116**. Likewise, the third and fourth bit lines **BL3** and **BL4** are both connected to a second precharge circuit **117** composed of two transistors **T17** and **T18**, and also connected to a second sense amplifier **118**. The third and fourth bit lines **BL3** and **BL4** serve as a bit line pair for the second sense amplifier **118**.

The ferroelectric memory device further includes a control circuit **119** for controlling the circuits described above. To be more specific, the control circuit **119** drives the first word line **WL1**, the second word line **WL2**, the first cell plate line **CP1**, the second cell plate line **CP2**, the first reference word line **RWL1**, the second reference word line **RWL2**, the first reference cell plate line **RCP1**, and the second reference cell plate line **RCP2**. Further, the control circuit **119** controls actions performed by each memory cell and each reference cell.

The control circuit **119** controls the first and third reset circuits **109** and **111** with a first reset control signal **RPG1**, the second and fourth reset circuits **110** and **112** with a second reset control signal **RPG2**, the first switch circuit **113** with a first switch control signal **REQ1**, the second switch circuit **114** with a second switch control signal **REQ2**, the first and second precharge circuits **115** and **117** with a precharge signal **BP**, and the first and second sense amplifiers **116** and **118** with a sense amplifier driving signal **SAE**.

The read operation in the conventional ferroelectric memory device will be described below with reference to the accompanying drawing. The following description using FIG. 10 is about the case where data is read out of the first and third memory cells **101** and **103**, provided that the first and third memory cells **101** and **103** retain “1” data and

“0” data, respectively, and the second and fourth reference cells **106** and **108** retain “1” data and “0” data, respectively.

Note that the memory cells and the reference cells retain “1” data when the ferroelectric capacitors **C1** to **C8** thereof have remnant polarization with their first electrodes being positive electrodes, and that they retain “0” data when the ferroelectric capacitors **C1** to **C8** thereof have remnant polarization with their second electrodes being positive electrodes.

FIG. 10 shows timings of the read operation in the conventional ferroelectric memory device. As shown in FIG. 10, first, in the initial state of the reading operation in this device, the bit line precharge signal **BP** is activated (a logical voltage of “H” level). The activated signal drives the first and second precharge circuits **115** and **117** to precharge the corresponding bit lines (specifically, the first, second, third and fourth bit lines **BL1**, **BL2**, **BL3** and **BL4**) at the ground voltage **Vss**. In this state, the first word line **WL1**, the first cell plate line **CP1**, the second reference word line **RWL2**, the second reference cell plate line **RCP2**, the second switch control signal **REQ2**, the second reset control signal **RPG2**, the reset data signal **RPD**, and the sense amplifier driving signal **SAE** stay inactivated (a logical voltage of “L” level).

Next, the bit line precharge signal **BP** is inactivated at the timing of time **t1**, whereby the bit lines **BL1** to **BL4** are made floating.

Then, at the timing of time **t2**, the second switch control signal **REQ2**, the first word line **WL1**, the first cell plate line **CP1**, the second reference word line **RWL2**, and the second reference cell plate line **RCP2** are activated.

In response, the transistors **T1** and **T3** are turned on and a voltage of “H” level is applied to the second electrodes of the ferroelectric capacitors **C1** and **C3**. Then, “1” data retained in the first memory cell **101** is supplied to the first bit line **BL1** and “0” data retained in the third memory cell **103** is supplied to the third bit line **BL3**. In addition, the transistors **T6** and **T8** are turned on and a voltage of “H” level is applied to the second

electrodes of the ferroelectric capacitors **C6** and **C8**. Then, “1” data retained in the second reference cell **106** is supplied to the second bit line **BL2** and “0” data retained in the fourth reference cell **108** is supplied to the fourth bit line **BL4**.

At this timing, the activated second switch control signal **REQ2** drives the second
5 switch circuit **114** to equalize the second and fourth bit lines **BL2** and **BL4**. As a result, the second and fourth bit lines **BL2** and **BL4** are supplied with an intermediate potential between the potential corresponding to “1” data and the potential corresponding to “0” data, which serves as a reference potential (reference level).

Next, at the timing of time **t3**, the first cell plate line **CP1** and the second reference
10 cell plate line **RCP2** are inactivated.

Then, at the timing of time **t4**, the sense amplifier driving signal **SAE** is activated to drive the first and second sense amplifiers **116** and **118**. In response, a potential difference across the first and second bit lines **BL1** and **BL2** is amplified so that the voltage value of the first bit line **BL1** is equal to the source voltage **Vcc** and the voltage
15 value of the second bit line **BL2** is equal to the ground voltage **Vss**. Simultaneously, a potential difference across the third and fourth bit lines **BL3** and **BL4** is amplified so that the voltage value of the third bit line **BL3** is equal to the ground voltage **Vss** and the voltage value of the fourth bit line **BL4** is equal to the source voltage **Vcc**.

At this timing, the first word line **WL1** stays activated, so that the source voltage
20 **Vcc** and the ground voltage **Vss** are supplied to the first electrodes of the ferroelectric capacitors **C1** and **C3** through the transistors **T1** and **T3**, respectively. Thus, rewriting in the first and third memory cells **101** and **103** is performed.

Subsequently to this series of actions, the second reference word line **RWL2** and the second switch control signal **REQ2** are successively inactivated. In response, the
25 transistors **T6** and **T8** are turned off to separate the second and fourth reference cells **106** and **108** from the second and fourth bit lines **BL2** and **BL4**, respectively, after which the

second switch circuit **114** is stopped to separate the second bit line **BL2** from the fourth bit line **BL4**.

Next, the reset data signal **RPD** and the second reset control signal **RPG2** are successively activated, thereby performing rewriting in the second and fourth reference cells **106** and **108** by using the second and fourth reset circuits **110** and **112**. In this rewriting, the first electrode of the ferroelectric capacitor **C8** of the fourth reference cell **108** is supplied with the ground voltage **Vss**, so that “0” data is written in the fourth reference cell **108**. On the other hand, the first electrode of the ferroelectric capacitor **C6** of the second reference cell **106** is supplied with a voltage of “H” level serving as the reset data signal **RPD**, so that “1” data is written in the second reference cell **106**.

Next, at the timing of time **t5**, the sense amplifier driving signal **SAE** is inactivated to stop the drive of the first and second sense amplifiers **116** and **118**, after which the second reference cell plate line **RCP2** is activated. In response, of the electrodes of the ferroelectric capacitor **C6** of the second reference cell **106**, the first electrode is supplied with a voltage of “H” level derived from the reset data signal **RPD**, and the second electrode is supplied with a voltage of “H” level derived from the second reference cell plate line **RCP2**. Therefore, the voltage applied to the ferroelectric capacitor **C8** of the fourth reference cell **108** becomes zero volts.

Thereafter, the bit line precharge signal **BP** is activated and in addition the second reference cell plate line **RCP2**, the first word line **WL1**, the reset data signal **RPD**, and the second reset control signal **RPG2** are successively inactivated to restore the device condition to the initial state. The read operation of the device is thus completed.

Next description using the drawings will be made of changes in charges stored in the ferroelectric capacitors during the read operation in the conventional ferroelectric memory device.

FIG. 11 is a graph showing the hysteresis properties of ferroelectric used in the ferroelectric capacitors of the conventional ferroelectric memory device. FIG. 11 plots the

voltage applied to the electrodes of each ferroelectric capacitor in abscissa and the polarization charge thereof in ordinate. In FIG. 11, a positive polarization charge represents the amount of the polarization charge in the case where the first electrodes of the ferroelectric capacitors **C1** to **C8** are used as positive electrodes.

5 As shown in FIG. 11, when the source voltage **Vcc** in the positive direction is applied to a ferroelectric capacitor, the capacitor stores a polarization charge corresponding to a point **A**. When the applied voltage is changed from this state in the negative direction, the ferroelectric capacitor stores a polarization charge corresponding to a point to which the point **A** moves along a curve **131** in the negative direction. In contrast, when the
10 source voltage **Vcc** in the negative direction is applied to the ferroelectric capacitor, the capacitor stores a polarization charge corresponding to a point **B**. When the applied voltage is changed from this state in the positive direction, the ferroelectric capacitor stores a polarization charge corresponding to a point to which the point **B** moves along a curve **132** in the positive direction.

15 The following description using FIG. 11 is about changes (the movement on FIG. 11) in polarization conditions of the ferroelectric capacitors in accordance with the timings of the read operation shown in FIG. 10.

 Note that “L” level in FIG. 10 is set at the ground potential value **Vss** (0 V) and “H” level in FIG. 10 is set at the source voltage value **Vcc**.

20 First, at the timing of the time **t1** in FIG. 10, no voltage is applied to the ferroelectric capacitors **C1** to **C8** of the memory cells and the reference cells. Therefore, in the first memory cell **101** and the second reference cell **106** both of which retain “1” data, the polarization charges of the ferroelectric capacitors **C1** and **C6** are located at a point **C** in FIG. 11. In the third memory cell **103** and the fourth reference cell **108** both of which
25 retain “0” data, the polarization charges of the ferroelectric capacitors **C3** and **C8** are located at a point **D** in FIG. 11.

At the timing of the time **t2** in FIG. 10, the transistors **T1** and **T3** are turned on and the source voltage **Vcc** is applied to the first cell plate line **CP1**. Then, the ground voltage **Vss** is applied to the first electrodes of the ferroelectric capacitors **C1** and **C3** and the source voltage **Vcc** is applied to the second electrodes of the ferroelectric capacitors **C1** and **C3**. Likewise, the transistors **T6** and **T8** are turned on and the source voltage **Vcc** as a voltage of “H” level is applied to the second reference cell plate line **RCP2**. Then, the ground voltage **Vss** is applied to the first electrodes of the ferroelectric capacitors **C6** and **C8** and the source voltage **Vcc** is applied to the second electrodes of the ferroelectric capacitors **C6** and **C8**. Each of the ferroelectric capacitors **C1**, **C3**, **C6** and **C8** then changes in the condition from the state in which no voltage is applied to the state in which a negative voltage ($-V_{cc}$) is applied thereto.

At this timing, in the first memory cell **101**, the polarization charge of the ferroelectric capacitor **C1** moves from the point **C** to a point **E** along the curve **131**. The point **E** is placed at the point determined by dividing the voltage **Vcc** applied to the ferroelectric capacitor **C1** in accordance with the capacitance of the first bit line **BL1** and the capacitance of the ferroelectric capacitor **C1**. To be more specific, the point to which the point **C** moves along the voltage axis in the negative direction by the voltage **Vcc** is defined as a point **F**, and a capacitance load line **133a** of the first bit line **BL1** is drawn from the point **F**. Thus, the point **E** is obtained as the intersection point of the capacitance load line **133a** with the curve **131**.

In the third memory cell **103**, the polarization charge of the ferroelectric capacitor **C3** moves from the point **D** along the curve **132** in the negative direction, and reaches to a point **H** which is located at the intersection point of the curve **132** with a capacitance load line **133c** of the third bit line **BL3** drawn from a point **G** to which the point **D** moves along the voltage axis in the negative direction by the voltage **Vcc**. Note that the capacitance of the third bit line **BL3** is equal to that of the first bit line **BL1**, so that the capacitance load

line **133c** of the third bit line **BL3** has the same inclination as the capacitance load line **133a** of the first bit line **BL1**.

Likewise, in the second reference cell **106**, the polarization charge of the ferroelectric capacitor **C6** moves from the point **C** to a point **I**, and in the fourth reference cell **108**, the polarization charge of the ferroelectric capacitor **C8** moves from the point **D** to a point **J**. Herein, the point **I** is located at the intersection point of the curve **131** with a capacitance load line **134a** of the second bit line **BL2**. The capacitance load line **134a** has a greater inclination than the capacitance load lines **133a** and **133c** because the second and fourth bit lines are equalized to increase the capacitance value of the second bit line.

At this timing, a charge **Q3** is read out on the first bit line **BL1**, and the first bit line **BL1** has a potential of “1” data corresponding to the point **E**. Also, a charge **Q2** is read out on the second and fourth bit lines **BL2** and **BL4**, and the second and fourth bit lines **BL2** and **BL4** have reference potentials corresponding to the points **I** and **J**. Further, a charge **Q1** is read out on the third bit line **BL3**, and the third bit line **BL3** has a potential of “0” data corresponding to the point **H**. As a result, a potential difference **V1** is created across the first and second bit lines **BL1** and **BL2**, and a potential difference **V2** is created across the third and fourth bit lines **BL3** and **BL4**.

Next, at the timing of the time **t3** in FIG. 10, the first cell plate line **CP1** and the second reference cell plate line **RCP2** are inactivated, so that in the first memory cell **101**, the third memory cell **103**, the second reference cell **106**, and the fourth reference cell **108**, the voltages applied to the respective ferroelectric capacitors change from the negative voltage ($-V_{cc}$) to zero volts.

By this change, in the first memory cell **101**, the polarization charge of the ferroelectric capacitor **C1** moves from the point **E** to a point **K** along a curve **135**. The point **K** is located at the intersection point of the curve **135** with a capacitance load line **133b** of the third bit line **BL1** drawn from a point **L** to which the point **E** moves along the voltage axis in the positive direction by the voltage **V_{cc}**. In the third memory cell **103**, the

polarization charge of the ferroelectric capacitor **C3** moves from the point **H** to the point **D** along the curve **132**.

Likewise, in the second reference cell **106**, the polarization charge of the ferroelectric capacitor **C6** moves from the point **I** to a point **M** along a curve **136**. The point **M** is located at the intersection point of the curve **136** with a capacitance load line **134b** of the second bit line **BL2** drawn from a point **N** to which the point **I** moves along the voltage axis in the positive direction by the voltage **Vcc**. In the fourth reference cell **108**, the polarization charge of the ferroelectric capacitor **C8** moves from the point **H** to a point **P** along the curve **132**.

At that time, a potential difference **V3** corresponding to the potential difference across the points **K** and **P** is created across the first and second bit lines **BL1** and **BL2**, and a potential difference **V4** corresponding to the potential difference across the points **D** and **P** is created across the third and fourth bit lines **BL3** and **BL4**.

Next, at the timing of the time **t4** in FIG. **10**, the potential difference **V4** is amplified by the first sense amplifier **116**, whereby the first bit line **BL1** has the source voltage **Vcc** and the second bit line **BL2** has the ground voltage **Vss**. Since the transistors **T1** and **T6** are on in this state, the ferroelectric capacitor **C1** of the first memory cell **101** has a positive voltage (**Vcc**) applied and the ferroelectric capacitor **C6** of the second reference cell **106** has a voltage of zero volts. Therefore, in the first memory cell **101**, the polarization charge of the ferroelectric capacitor **C1** moves from the point **K** to the point **A** along the curve **135**. In the second reference cell **106**, the polarization charge of the ferroelectric capacitor **C6** moves from the point **M** to a point **Q**.

Likewise, the potential difference **V3** is amplified by the second sense amplifier **118**, whereby the third bit line **BL3** has the ground voltage **Vss** and the fourth bit line **BL4** has the source voltage **Vcc**. Since the transistors **T3** and **T8** are on in this state, the ferroelectric capacitor **C3** of the third memory cell **103** keeps a voltage of zero volts and the polarization charge thereof does not move and remains at the point **D**. In the fourth

reference cell **108**, the ferroelectric capacitor **C8** thereof has the source voltage **Vcc** applied, so that the polarization charge thereof moves from the point **P** to the point **A**.

Subsequently, the reset data signal **RPD** and the second reset control signal **RPG2** are successively activated. Then, the source voltage **Vcc** derived from the reset data signal
5 **RPD** is applied to the first electrode of the ferroelectric capacitor **C6** of the second reference cell **106**, and the ground voltage **Vss** is applied to the ferroelectric capacitor **C8** of the fourth reference cell **108**. Therefore, the voltage applied to the ferroelectric capacitor **C6** is changed from zero volts to a positive voltage and the polarization charge thereof moves from the point **Q** to the point **A** along the curve **136**. In the ferroelectric
10 capacitor **C8** of the fourth reference cell **108**, the voltage applied to the ferroelectric capacitor **C8** is changed from the source voltage **Vcc** to zero volts and the polarization charge thereof moves from the point **A** to the point **C** along the curve **131**.

Next, the second reference cell plate line **RCP2** is activated subsequently to the timing of the time **t5** in FIG. **10**, whereby the source voltage **Vcc** is applied to the second
15 electrodes of the ferroelectric capacitors **C6** and **C8** of the second and fourth reference cells **106** and **108**. The voltage applied to the ferroelectric capacitor **C6** is then changed from a positive voltage to zero volts and the polarization charge thereof moves from the point **A** to the point **C** along the curve **131**. On the other hand, the voltage applied to the ferroelectric capacitor **C8** is then changed from zero volts to a negative voltage and the
20 polarization charge thereof moves from the point **C** to the point **B** along the curve **131**.

Thereafter, the reset data signal **RPD** and the second reset control signal **RPG2** are successively inactivated, so that the voltages of the first electrodes of the ferroelectric capacitors **C6** and **C8** become zero volts. The second reference cell plate line **RCP2** is inactivated, so that the voltages of the second electrodes of the ferroelectric capacitors **C6**
25 and **C8** become zero volts. From these actions, the ferroelectric capacitor **C6** of the second reference cell **106** keeps a voltage of zero volts and the polarization charge thereof remains at the point **C**. In the fourth reference cell **108**, the voltage applied to the ferroelectric

capacitor **C8** is then changed from a negative voltage to zero volts and the polarization charge thereof moves from the point **B** to the point **D** along the curve **132**.

As is apparent from the above, the read operation of the memory cells in the conventional ferroelectric memory device is accomplished so that in the memory cell retaining "1" data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order of the point **C**, the point **E**, the point **K**, the point **A**, and the point **C**, and that in the memory cell retaining "0" data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order of the point **D**, the point **H**, the point **B**, and the point **D**. The read operation of the reference cells is accomplished so that in the reference cell retaining "1" data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order of the point **C**, the point **I**, the point **M**, the point **Q**, the point **A**, and the point **C**, and that in the reference cell retaining "0" data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order of the point **D**, the point **J**, the point **P**, the point **A**, the point **B**, and the point **D**. In this read operation, the amount of charge for polarization reversal in the ferroelectric capacitor retaining "0" data is equal to the charge amount **QSW** between the point **C** and the point **D** shown in FIG. 11.

The conventional ferroelectric memory device described above, however, has a problem relating to the properties of the number of rewriting operations. In a number of memory cells provided on a single bit line pair, every time one memory cell is read out, one reference cell pair operates for the reading. This greatly increases the number of times each reference cell operates as compared with the number of times each memory cell operates. As a result, the properties of the number of rewriting operations in the ferroelectric memory device decrease depending upon the degradation of the reference cells.

SUMMARY OF THE INVENTION

An object of the present invention is to solve the foregoing problem, and to provide a ferroelectric memory device generating a reference potential with reference cells and having enhanced properties of the number of rewriting operations by decreasing the amount of charge for polarization reversal in the reference cells during the read operation
5 of the device.

To attain this object, a ferroelectric memory device of the present invention comprises: a plurality of bit line pairs each of which is composed of first and second bit lines; a plurality of sense amplifiers each for amplifying a potential difference across the corresponding bit line pair; a plurality of memory cells provided for the bit line pairs,
10 respectively, each of the memory cells being composed of a first ferroelectric capacitor for retaining data and a transistor whose source is connected to a first electrode of the first ferroelectric capacitor and whose drain is connected to the first bit line; a plurality of reference cells provided for the bit line pairs, respectively, each of the reference cells being composed of a second ferroelectric capacitor for retaining data and a transistor whose
15 source is connected to a first electrode of the second ferroelectric capacitor and whose drain is connected to the second bit line; a word line connecting gates of the transistors of the memory cells; a reference word line connecting gates of the transistors of the reference cells; a cell plate line connecting second electrodes of the ferroelectric capacitors of the memory cells; a reference cell plate line connecting second electrodes of the ferroelectric
20 capacitors of the reference cells; and a control circuit for controlling operations of the memory cells, the reference cells, and the sense amplifiers. In the ferroelectric memory device, the control circuit inactivates the reference word line during the drive of the sense amplifiers.

In the ferroelectric memory device of the present invention, the first electrode of
25 the ferroelectric capacitor in the reference cell is separated from the second bit line during the drive of the sense amplifier, which prevents the polarization charge of the ferroelectric capacitor in the reference cell from moving due to the potential amplified by the sense

amplifier. This decreases the amount of charge for polarization reversal in the reference cell, resulting in the reduction of stresses occurring in the ferroelectric capacitor of the reference cell during the read operation of the memory cell. Consequently, the properties of the number of rewriting operations can be enhanced in the ferroelectric memory device.

5 Preferably, the ferroelectric memory device of the present invention further comprises a switch circuit connecting the second bit lines included in adjacent bit line pairs of the plurality of bit line pairs. In the ferroelectric memory device, the control circuit stops the drive of the switch circuit during the drive of the sense amplifiers.

10 With this configuration, the reference voltage for the sense amplifiers is generated by connecting two second bit lines, and the sense amplifiers are driven while the two bit lines are kept separated. This minimizes the power consumption of the ferroelectric memory device.

15 Preferably, in the ferroelectric memory device of the present invention, the control circuit performs successive actions of: driving the switch circuit and activating the word line, the cell plate line, the reference word line and the reference cell plate line; inactivating the cell plate line and the reference cell plate line; inactivating the reference word line; stopping the drive of the switch circuit; and driving the sense amplifiers.

20 With this sequence, the switch circuit is driven before the reference word line is activated, so that noises caused in stopping the drive of the switch circuit are not transferred to the ferroelectric capacitor. This prevents the polarization charge of the ferroelectric capacitor from moving due to the noises accompanied with the inactivation of the switch control signal. In particular, when the capacitances of the bit lines are large, the noises accompanied with the suspension of the switch circuit have a little effect on the potentials of the bit lines. This enables a reliable read operation in the ferroelectric
25 memory device.

 Preferably, in the ferroelectric memory device of the present invention, the control circuit performs successive actions of: driving the switch circuit and activating the word

line, the cell plate line, the reference word line and the reference cell plate line; inactivating the cell plate line and the reference cell plate line; stopping the drive of the switch circuit; inactivating the reference word line; and driving the sense amplifiers.

With this sequence, the reference word line is inactivated after the drive of the switch circuit is stopped. Therefore, in the case of small capacitances of the bit lines, noises accompanied with the suspension of the switch circuit have a little effect on the bit lines, which enables a reliable read operation in the ferroelectric memory device.

Preferably, in the ferroelectric memory device of the present invention, the control circuit performs successive actions of: driving the switch circuit and activating the word line, the cell plate line, the reference word line and the reference cell plate line; inactivating the reference word line; stopping the drive of the switch circuit; inactivating the cell plate line and the reference cell plate line; and driving the sense amplifiers.

With this sequence, the cell plate line and the reference cell plate line are kept activated even during the drive of the sense amplifier, which raises the potential of the bit line in stopping the drive of the switch circuit. Therefore, it is possible to reduce the effect of noises on the ferroelectric memory device.

Preferably, in the ferroelectric memory device of the present invention, the control circuit performs successive actions of: driving the switch circuit and activating the word line, the cell plate line, the reference word line and the reference cell plate line; stopping the drive of the switch circuit; inactivating the reference word line; inactivating the cell plate line and the reference cell plate line; and driving the sense amplifiers.

Preferably, in the ferroelectric memory device of the present invention, the control circuit performs successive actions of: driving the switch circuit; and activating the word line, the cell plate line, the reference word line and the reference cell plate line.

With this sequence, the cell plate line and the reference cell plate line are activated with the driving time of the switch circuit secured, which reduces the time that elapsed before the potential used for reference is created. This makes it possible to operate the

ferroelectric memory device with high speed.

Preferably, in the ferroelectric memory device of the present invention, the control circuit performs successive actions of: activating the reference word line and the reference cell plate line for a predetermined period of time; driving the switch circuit for a
5 predetermined period of time; and driving the sense amplifiers.

With this sequence, the bit lines are equalized with the capacitance of the ferroelectric capacitor not added to the bit lines. This decreases the amount of charge for polarization reversal to a further extent, and in addition generates a reference potential accurately. This further enhances the properties of the number of rewriting operations and
10 the reliability of the read operation of the ferroelectric memory device.

A method for reading data from a ferroelectric memory device of the present invention employs a ferroelectric memory device including: a plurality of bit line pairs each of which is composed of first and second bit lines; a plurality of sense amplifiers each for amplifying a potential difference across the corresponding bit line pair; a plurality of
15 memory cells provided for the bit line pairs, respectively, each of the memory cells being composed of a first ferroelectric capacitor for retaining data and a transistor whose source is connected to a first electrode of the first ferroelectric capacitor and whose drain is connected to the first bit line; a plurality of reference cells provided for the bit line pairs, respectively, each of the reference cells being composed of a second ferroelectric capacitor
20 for retaining data and a transistor whose source is connected to a first electrode of the second ferroelectric capacitor and whose drain is connected to the second bit line; a word line connecting gates of the transistors of the memory cells; a reference word line connecting gates of the transistors of the reference cells; a cell plate line connecting second electrodes of the ferroelectric capacitors of the memory cells; a reference cell plate line
25 connecting second electrodes of the ferroelectric capacitors of the reference cells; a control circuit for controlling operations of the memory cells, the reference cells, and the sense amplifiers; and a switch circuit connecting the second bit lines included in adjacent bit line

pairs of the plurality of bit line pairs. The method comprises: a first step of activating the word line and the reference word line; a second step of activating the cell plate line and the reference cell plate line for a predetermined period of time; a third step of activating a switch control signal for driving the switch circuit; a fourth step of inactivating the reference word line after the first step; a fifth step of inactivating the switch control signal after the third step; and a sixth step of driving the sense amplifier for a predetermined period of time after the fourth step.

In this method, the first electrode of the ferroelectric capacitor in the reference cell is separated from the second bit line during the drive of the sense amplifier, which prevents the polarization charge of the ferroelectric capacitor in the reference cell from moving due to the potential amplified by the sense amplifier. This decreases the amount of charge for polarization reversal in the reference cell, resulting in the reduction of stresses occurring in the ferroelectric capacitor of the reference cell during the read operation of the memory cell. Consequently, the properties of the number of rewriting operations can be enhanced in the ferroelectric memory device.

In the method for reading a ferroelectric memory device according to the present invention, the sixth step is preferably performed after the fifth step.

With this method, the sense amplifier is driven while the two bit lines supplied with different pieces of data are kept separated. This minimizes the power consumption of the ferroelectric memory device.

In the method for reading a ferroelectric memory device according to the present invention, the fifth step is preferably performed after the fourth step.

With this method, the switch control signal is inactivated after the reference word line is inactivated, so that noises caused in the inactivation of the switch control signal are not transferred to the ferroelectric capacitor. This prevents the polarization charge of the ferroelectric capacitor from moving due to the noises accompanied with the inactivation of the switch control signal. In particular, when the capacitances of the bit lines are large, the

noises accompanied with the inactivation of the switch control signal have a little effect on the potentials of the bit lines. This enables a reliable read operation in the ferroelectric memory device.

In the method for reading a ferroelectric memory device according to the present invention, the fifth step is preferably performed before the fourth step.

With this method, the reference word line is inactivated after the inactivation of the switch control signal. Therefore, in the case of small capacitances of the bit lines, noises accompanied with the inactivation of the switch control signal have a little effect on the bit lines, which enables a reliable read operation in the ferroelectric memory device.

In the method for reading a ferroelectric memory device according to the present invention, the second step is preferably kept on until after the initiation of the sixth step.

With this method, the cell plate line and the reference cell plate line are kept activated even during the drive of the sense amplifier, which raises the potential of the bit line in the inactivation of the switch control signal.

In the method for reading a ferroelectric memory device according to the present invention, the first step is preferably performed after the third step.

With this method, the cell plate line and the reference cell plate line are activated with the equalization time secured by the activation of the switch control signal, which reduces the time that elapsed before the potential of the bit line becomes a reference potential. This makes it possible to operate the ferroelectric memory device with high speed.

In the method for reading a ferroelectric memory device according to the present invention, the third step is preferably performed after the fourth step.

With this method, the bit lines are equalized with the capacitance of the ferroelectric capacitor not added to the bit lines, which decreases the amount of charge for polarization reversal to a further extent, and in addition generates a reference potential accurately. This further enhances the properties of the number of rewriting operations and

the reliability of the read operation of the ferroelectric memory device.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a circuit diagram showing a ferroelectric memory device according to a
5 first embodiment of the present invention.

FIG. 2 is a timing chart showing timings of the read operation in the ferroelectric memory device according to the first embodiment of the present invention.

FIG. 3 is a graph showing the hysteresis properties of ferroelectric capacitors in the ferroelectric memory device according to the first embodiment of the present invention.

10 FIG. 4 is a timing chart showing timings of the read operation in a ferroelectric memory device according to a modification of the first embodiment of the present invention.

FIG. 5 is a timing chart showing timings of the read operation in a ferroelectric memory device according to a second embodiment of the present invention.

15 FIG. 6 is a timing chart showing timings of the read operation in a ferroelectric memory device according to a third embodiment of the present invention.

FIG. 7 is a timing chart showing timings of the read operation in a ferroelectric memory device according to a fourth embodiment of the present invention.

20 FIG. 8 is a timing chart showing timings of the read operation in a ferroelectric memory device according to a fifth embodiment of the present invention.

FIG. 9 is a circuit diagram showing a conventional ferroelectric memory device.

FIG. 10 is a timing chart showing timings of the read operation in the conventional ferroelectric memory device.

25 FIG. 11 is a graph showing the hysteresis properties of ferroelectric capacitors in the conventional ferroelectric memory device.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

(First Embodiment)

A ferroelectric memory device according to a first embodiment of the present invention will now be described with reference to the accompanying drawings.

FIG. 1 shows a circuit configuration of the ferroelectric memory device according to the first embodiment. Referring to FIG. 1, the ferroelectric memory device of the first embodiment includes first, second, third and fourth memory cells 11, 12, 13 and 14 as memory cells for retaining data. The first memory cell 11 is composed of a transistor T1 whose gate is connected to a first word line WL1 and whose drain is connected to a first bit line BL1, and a ferroelectric capacitor C1 whose first electrode is connected to a source of the transistor T1 and whose second electrode is connected to a first cell plate line CP1. The second memory cell 12 is composed of a transistor T2 whose gate is connected to a second word line WL2 and whose drain is connected to a second bit line BL2, and a ferroelectric capacitor C2 whose first electrode is connected to a source of the transistor T2 and whose second electrode is connected to a second cell plate line CP2. The third memory cell 13 is composed of a transistor T3 whose gate is connected to the first word line WL1 and whose drain is connected to a third bit line BL3, and a ferroelectric capacitor C3 whose first electrode is connected to a source of the transistor T3 and whose second electrode is connected to the first cell plate line CP1. The fourth memory cell 14 is composed of a transistor T4 whose gate is connected to the second word line WL2 and whose drain is connected to a fourth bit line BL4, and a ferroelectric capacitor C4 whose first electrode is connected to a source of the transistor T4 and whose second electrode is connected to the second cell plate line CP2.

The ferroelectric memory device of the first embodiment further includes first, second, third and fourth reference cells 15, 16, 17 and 18 as memory cells for retaining data used in the generation of a reference potential (reference level). The first reference cell 15 is composed of a transistor T5 whose gate is connected to a first reference word line RWL1 and whose drain is connected to the first bit line BL1, and a ferroelectric

capacitor **C5** whose first electrode is connected to a source of the transistor **T5** and whose second electrode is connected to a first reference cell plate line **RCP1**. The second reference cell **16** is composed of a transistor **T6** whose gate is connected to a second reference word line **RWL2** and whose drain is connected to the second bit line **BL2**, and a
5 ferroelectric capacitor **C6** whose first electrode is connected to a source of the transistor **T6** and whose second electrode is connected to a second reference cell plate line **RCP2**. The third reference cell **17** is composed of a transistor **T7** whose gate is connected to the first reference word line **RWL1** and whose drain is connected to the third bit line **BL3**, and a
10 ferroelectric capacitor **C7** whose first electrode is connected to a source of the transistor **T7** and whose second electrode is connected to the first reference cell plate line **RCP1**. The fourth reference cell **18** is composed of a transistor **T8** whose gate is connected to the second reference word line **RWL2** and whose drain is connected to the fourth bit line **BL4**, and a ferroelectric capacitor **C8** whose first electrode is connected to a source of the transistor **T8** and whose second electrode is connected to the second reference cell plate
15 line **RCP2**.

The first to fourth reference cells **15** to **18** are provided with first to fourth reset circuits **19** to **22**, respectively, as circuits for writing predetermined pieces of data in the respective cells. The first to fourth reset circuits **19** to **22** are composed of transistors **T9** to **T12** whose drains are connected to the first electrodes of the ferroelectric capacitors **C5** to
20 **C8**, respectively.

The first and third bit lines **BL1** and **BL3** are connected to each other through a first switch circuit **23** composed of a transistor **T13**. The second and fourth bit lines **BL2** and **BL4** are connected to each other through a second switch circuit **24** composed of a transistor **T14**.

25 The first and second bit lines **BL1** and **BL2** are both connected to a first precharge circuit **25** composed of two transistors **T15** and **T16**, and also connected to a first sense amplifier **26**. The first and second bit lines **BL1** and **BL2** serve as a bit line pair for the

first sense amplifier **26**. Likewise, the third and fourth bit lines **BL3** and **BL4** are both connected to a second precharge circuit **27** composed of two transistors **T17** and **T18**, and also connected to a second sense amplifier **28**. The third and fourth bit lines **BL3** and **BL4** serve as a bit line pair for the second sense amplifier **28**.

5 The ferroelectric memory device further includes a control circuit **29** for controlling the circuits described above.

To be more specific, the control circuit **29** drives the first word line **WL1**, the first cell plate line **CP1**, the second word line **WL2**, the second cell plate line **CP2**, the first reference word line **RWL1**, the first reference cell plate line **RCP1**, the second reference
10 word line **RWL2**, and the second reference cell plate line **RCP2**. Further, the control circuit **29** controls the output of data retained in each memory cell and each reference cell to the corresponding bit line.

The control circuit **29** supplies a first reset control signal **RPG1** to the gates of the transistors **T9** and **T11** to drive the first and third reset circuits **19** and **21**, respectively, and
15 supplies a second reset control signal **RPG2** to the gates of the transistors **T10** and **T12** to drive the second and fourth reset circuits **20** and **22**, respectively. The control circuit **29** thus controls data rewriting in each reference cell.

In this control, for the first and fourth reset circuits **19** and **22**, a reset data signal **RPD** is supplied to the sources of the transistors **T9** and **T12** thereof. For the second and
20 third reset circuits **20** and **21**, a ground voltage **Vss** is supplied to the sources of the transistors **T10** and **T11** thereof. Therefore, data written in the first and fourth reset circuits **19** and **22** are different from data written in the second and third reset circuits **20** and **21**.

The control circuit **29** supplies a first switch control signal **REQ1** to the gate of the
25 transistor **T13** to drive the first switch circuit **23**, thereby bringing the first and third bit lines **BL1** and **BL3** into conduction. Likewise, the control circuit **29** supplies a second

switch control signal **REQ2** to the gate of the transistor **T14** to drive the second switch circuit **24**, thereby bringing the second and fourth bit lines **BL2** and **BL4** into conduction.

The control circuit **29** supplies a precharge signal **BP** to the gates of the transistors **T15** to **T18** to control the first and second precharge circuits **25** and **27**, thereby
5 precharging the first to fourth bit lines **BL1** to **BL4** at the ground voltage **Vss**.

The control circuit **29** activates a sense amplifier driving signal **SAE** to drive the first sense amplifier **26**, thereby amplifying the potential difference across the bit line pair composed of the first and second bit lines **BL1** and **BL2**. Likewise, the control circuit **29** activates the sense amplifier driving signal **SAE** to drive the second sense amplifier **28**,
10 thereby amplifying the potential difference across the bit line pair composed of the third and fourth bit lines **BL3** and **BL4**.

The device configuration described above accomplishes the data reading in the first and third memory cells **11** and **13** in such a manner that the second and fourth bit lines **BL2** and **BL4** are equalized by the first switch circuit **23** to supply, to the second and
15 fourth bit lines **BL2** and **BL4**, an intermediate potential between the potential corresponding to the data retained by the second reference cell **16** and the potential corresponding to the data retained by the fourth reference cell **18**, which serves as a reference potential.

Also, the device configuration described above accomplishes the data reading in the
20 second and fourth memory cells **12** and **14** in such a manner that the first and third bit lines **BL1** and **BL3** are equalized by the second switch circuit **24** to supply, to the first and third bit lines **BL1** and **BL3**, an intermediate potential between the potential corresponding to the data retained by the first reference cell **15** and the potential corresponding to the data retained by the third reference cell **17**, which serves as a reference potential.

25 In the ferroelectric memory device of the first embodiment shown in FIG. 1, the bit lines **BL1** to **BL4** are each provided in plurality across the word lines, and the memory cells are each provided in plurality along the bit lines.

In this device, various circuits are formed between the bit line pair composed of the first and second bit lines **BL1** and **BL2** and between the bit line pair composed of the third and fourth bit lines **BL3** and **BL4**. One said pair has the same circuit arrangement as the other said pair except that in the adjacent bit line pairs, the reset circuits for receiving the reset data signal **RPD** and the reset circuits for receiving the ground potential **Vss** are reversed in position. This enables the retention of different data in the reference cells provided on the two bit lines in the adjacent bit line pairs which are connected to each other by the switch circuit.

Note that for each of the bit line pairs composed of the first and second bit lines **BL1** and **BL2** and composed of the third and fourth bit lines **BL3** and **BL4** in the device of the first embodiment in FIG. 1, a memory cell and a reference cell are not necessarily formed on the both bit lines of each pair. The reference cell need only be formed on the bit line different from the bit line for reading data in the memory cell.

For example, in the bit line pair composed of the first and second bit lines **BL1** and **BL2**, the second memory cell **12** and the first reference cell **15** may be absent. In this case, the second switch circuit **24** enables equalization of the second reference cell **16** with the fourth reference cell **18** which is a reference cell on the adjacent bit line pair, thereby supplying a reference potential to the second bit line **BL2**.

In the ferroelectric memory device of the first embodiment shown in FIG. 1, the first reference cell **15** and the fourth reference cell **18** are connected to the ground potential line **Vss** through the first reset circuit **19** and the fourth reset circuit **22**, respectively, and the second reference cell **16** and the third reference cell **17** are connected to the reset data signal line **RPD** through the second reset circuit **20** and the third reset circuit **21**, respectively. However, the device configuration is not limited to this. Alternatively, reference cells provided on two bit lines connected to each other through a switch circuit need only have different data written.

The read operation in the ferroelectric memory device according to the first embodiment will be described below with reference to the accompanying drawing. The following description employs an exemplary device configuration such that signals generated by the control circuit 29 use a positive source voltage V_{cc} for a logical voltage of “H” level and a ground voltage V_{ss} of zero volts for a logical voltage of “L” level. Also in this configuration, the memory cells and the reference cells retain “1” data when the ferroelectric capacitors C1 to C8 thereof have remnant polarization with their first electrodes being positive electrodes, and they retain “0” data when the ferroelectric capacitors C1 to C8 thereof have remnant polarization with their second electrodes being positive electrodes.

The description that follows is about the read operation of the first and third memory cells 11 and 13 where the first and third memory cells 11 and 13 retain “1” data and “0” data, respectively, and the second and fourth reference cells 16 and 18 have “1” data and “0” data written in advance, respectively.

FIG. 2 shows timings of the read operation in the ferroelectric memory device of the first embodiment. As shown in FIG. 2, first, in the initial state of the reading operation in the ferroelectric memory device of the first embodiment, the bit line precharge signal BP is activated (a logical voltage of “H” level). The activated signal drives the first and second precharge circuits 25 and 27 to precharge the corresponding bit lines (specifically, the first, second, third and fourth bit lines BL1, BL2, BL3 and BL4) at the ground voltage V_{ss} .

In this state, the first word line WL1, the first cell plate line CP1, the second reference word line RWL2, the second reference cell plate line RCP2, the second switch control signal REQ2, the second reset control signal RPG2, the reset data signal RPD, and the sense amplifier driving signal SAE stay inactivated (a logical voltage of “L” level).

Although not shown in this figure, no read operation of the second and fourth memory cells 12 and 14 is done during the read operation of the first and third memory

cells **11** and **13**. Therefore, the second word line **WL2**, the second cell plate line **CP2**, the first reference word line **RWL1**, the first reference cell plate line **RCP1**, the first switch control signal **REQ1**, and the first reset control signal **RPG1** are kept inactivated.

Next, the bit line precharge signal **BP** is inactivated at the timing of time **t1**,
5 whereby the bit lines **BL1** to **BL4** are made floating.

Then, at the timing of time **t2**, the second switch control signal **REQ2**, the first word line **WL1**, the first cell plate line **CP1**, the second reference word line **RWL2**, and the second reference cell plate line **RCP2** are made activated.

In response, the transistors **T1** and **T3** are turned on and a voltage of “H” level used
10 for data reading is applied to the second electrodes of the ferroelectric capacitors **C1** and **C3**. Then, a potential corresponding to “1” data retained in the first memory cell **11** is supplied to the first bit line **BL1** and a potential corresponding to “0” data retained in the third memory cell **13** is supplied to the third bit line **BL3**. The values of the potentials received by the bit lines are determined by dividing the voltages for the data reading
15 applied to the second electrodes of the ferroelectric capacitors **C1** and **C3** in accordance with the capacitances of the bit lines and the capacitances of the ferroelectric capacitors **C1** and **C3**, respectively. As a result, a voltage according to the data retained in each memory cell is supplied to the corresponding bit line.

Likewise, the transistors **T6** and **T8** are turned on and a voltage of “H” level is
20 applied to the second electrodes of the ferroelectric capacitors **C6** and **C8**. Then, “1” data retained in the second reference cell **16** is supplied to the second bit line **BL2** and “0” data retained in the fourth reference cell **18** is supplied to the fourth bit line **BL4**.

At this timing, the activated second switch control signal **REQ2** drives the second switch circuit **24**, thereby equalizing the second and fourth bit lines **BL2** and **BL4**. As a
25 result, the second and fourth bit lines **BL2** and **BL4** are supplied with an intermediate potential between the potential corresponding to “1” data and the potential corresponding to “0” data, which serves as a reference potential.

Note that in FIG. 2, the first word line **WL1** and the second reference word line **RWL2** become activated before the time **t2**. Alternatively, the two lines may be activated concurrently with the first cell plate line **CP1** and the second reference cell plate line **RCP2**.

5 Next, at the timing of time **t3**, the first cell plate line **CP1** and the second reference cell plate line **RCP2** are inactivated. This stops voltage supply to the second electrodes of the ferroelectric capacitors **C1** and **C3** and the second electrodes of the ferroelectric capacitors **C6** and **C8**, which stops data output from the first and third memory cells **11** and **13** and the second and fourth reference cells **16** and **18** to the respective bit lines **BL1**
10 to **BL4**.

Subsequently to this action and prior to the timing of time **t4**, the second reference word line **RWL2** and the second switch control signal **REQ2** are successively inactivated. In response, the transistors **T6** and **T8** are turned off to separate the second and fourth reference cells **16** and **18** from the second and fourth bit lines **BL2** and **BL4**, respectively,
15 after which the second switch circuit **24** is stopped to separate the second bit line **BL2** from the fourth bit line **BL4**.

Then, at the timing of time **t4**, the sense amplifier driving signal **SAE** is activated to drive the first and second sense amplifiers **26** and **28**. In response, a potential difference across the first and second bit lines **BL1** and **BL2** is amplified so that the voltage value of
20 the first bit line **BL1** is equal to the source voltage **Vcc** and the voltage value of the second bit line **BL2** is equal to the ground voltage **Vss**. Simultaneously, a potential difference across the third and fourth bit lines **BL3** and **BL4** is amplified so that the voltage value of the third bit line **BL3** is equal to the ground voltage **Vss** and the voltage value of the fourth bit line **BL4** is equal to the source voltage **Vcc**.

25 At this timing, the first word line **WL1** stays activated, so that the source voltage **Vcc** and the ground voltage **Vss** are supplied to the first electrodes of the ferroelectric

capacitors **C1** and **C3** through the transistors **T1** and **T3**, respectively. Thus, rewriting in the first and third memory cells **11** and **13** is performed.

In this state, during the drive of the first and second sense amplifiers **26** and **28**, the second bit line **BL2** with the second reference cell **16** connected thereto is separated from the fourth bit line **BL4** with the fourth reference cell **18** connected thereto. This minimizes the current consumption in the device as compared with a conventional ferroelectric memory device which drives sense amplifiers and simultaneously equalizes bit lines to which reference cells retaining different pieces of data are connected.

Subsequently to this series of actions, the reset data signal **RPD** and the second reset control signal **RPG2** are successively activated, thereby performing rewriting in the second and fourth reference cells **16** and **18** by utilizing the second and fourth reset circuits **20** and **22**. In this rewriting, the first electrode of the ferroelectric capacitor **C8** of the fourth reference cell **18** is supplied with the ground voltage **Vss**, so that "0" data is written in the fourth reference cell **18**. On the other hand, the first electrode of the ferroelectric capacitor **C6** of the second reference cell **16** is supplied with a voltage of "H" level serving as a reset data signal **RPD**, so that "1" data is written in the second reference cell **16**.

Next, at the timing of time **t5**, the sense amplifier driving signal **SAE** is inactivated to stop the drive of the first and second sense amplifiers **26** and **28**, after which the second reference cell plate line **RCP2** is activated. In response, of the electrodes of the ferroelectric capacitor **C6** of the second reference cell **16**, the first electrode is supplied with a voltage of "H" level derived from the reset data signal **RPD**, and the second electrode is supplied with a voltage of "H" level derived from the second reference cell plate line **RCP2**. Therefore, the voltage applied to the ferroelectric capacitor **C6** of the second reference cell **16** becomes zero volts.

Thereafter, the bit line precharge signal **BP** is activated and in addition the second reference cell plate line **RCP2**, the first word line **WL1**, the reset data signal **RPD**, and the

second reset control signal **RPG2** are successively inactivated to restore the device condition to the initial state. The read operation of the device is thus completed.

The foregoing description has been made of the read operation of the first and third memory cells **11** and **13**. In the case where the second and fourth memory cells **12** and **14** are read out, "0" data retained in the first reference cell **15** is read out on the first bit line **BL1**, and "1" data retained in the third reference cell **17** is read out on the third bit line **BL3**. Then, the first switch circuit **23** is driven to supply the first and third bit lines **BL1** and **BL3** with the reference potential. The read operation of the second and fourth memory cells **12** and **14** is thus accomplished.

Next description using the drawings will be made of changes in polarization charges of the ferroelectric capacitors accompanied with the read operation in the ferroelectric memory device of the first embodiment.

FIG. 3 is a graph showing the changes (movement on **FIG. 3**) in the polarization charges of the ferroelectric capacitors accompanied with the read operation in the ferroelectric memory device of the first embodiment, and also showing the hysteresis properties of ferroelectric used in the ferroelectric capacitors. **FIG. 3** plots the voltage applied to each ferroelectric capacitor in abscissa and the polarization charge thereof in ordinate. In **FIG. 3**, a positive polarization charge represents the amount of the polarization charge in the case where the first electrodes of the ferroelectric capacitors **C1** to **C8** are used as positive electrodes.

As shown in **FIG. 3**, when the source voltage **Vcc** in the positive direction is applied to a ferroelectric capacitor, the capacitor stores a polarization charge corresponding to a point **A**. When the applied voltage is changed from this state in the negative direction, the ferroelectric capacitor stores a polarization charge corresponding to a point to which the point **A** moves along a curve **31** in the negative direction. In contrast, when the source voltage **Vcc** in the negative direction is applied to the ferroelectric capacitor, the capacitor stores a polarization charge corresponding to a point **B**. When the applied voltage is

changed from this state in the positive direction, the ferroelectric capacitor stores a polarization charge corresponding to a point to which the point **B** moves along a curve **32** in the positive direction.

The following description using FIG. 3 is about the movement on FIG. 3 of the polarization charges of the ferroelectric capacitors in accordance with the timings of the read operation shown in FIG. 2.

Note that “L” level in FIG. 2 is set at the ground potential value V_{ss} (0 V) and “H” level in FIG. 2 is set at the source voltage value V_{cc} (> 0 V).

First, at the timing of the time t_1 in FIG. 2, no voltage is applied to the ferroelectric capacitors **C1** to **C8** of the memory cells and the reference cells. Therefore, in the first memory cell **11** and the second reference cell **16** both of which retain “1” data, the polarization charges of the ferroelectric capacitors **C1** and **C6** are located at a point **C** in FIG. 3. In the third memory cell **13** and the fourth reference cell **18** both of which retain “0” data, the polarization charges of the ferroelectric capacitors **C3** and **C8** are located at a point **D** in FIG. 3.

At the timing of the time t_2 in FIG. 2, the transistors **T1** and **T3** are turned on and the source voltage V_{cc} as a voltage of “H” level is applied to the first cell plate line **CP1**. Then, the ground voltage V_{ss} is applied to the first electrodes of the ferroelectric capacitors **C1** and **C3** and the source voltage V_{cc} is applied to the second electrodes of the ferroelectric capacitors **C1** and **C3**.

At this timing, in the first memory cell **11**, the polarization charge of the ferroelectric capacitor **C1** moves from the point **C** to a point **E** along the curve **31**. The point **E** is placed at the point determined by dividing the voltage V_{cc} applied to the ferroelectric capacitor **C1** in accordance with the capacitance of the first bit line **BL1** and the capacitance of the ferroelectric capacitor **C1**. To be more specific, the point to which the point **C** moves along the voltage axis in the negative direction by the source voltage V_{cc} is defined as a point **F**, and a capacitance load line **33a** of the first bit line **BL1** is

drawn from the point **F**. Thus, the point **E** is obtained as the intersection point of the capacitance load line **33a** with the curve **31**.

In the third memory cell **13**, the polarization charge of the ferroelectric capacitor **C3** moves from the point **D** along the curve **32** in the negative direction, and reaches a point **H** which is located at the intersection point of the curve **32** with a capacitance load line **33c** of the third bit line **BL3** drawn from a point **G** to which the point **D** moves along the voltage axis in the negative direction by the voltage **Vcc**. Note that the capacitance of the third bit line **BL3** is equal to that of the first bit line **BL1**, so that the capacitance load line **33c** of the third bit line **BL3** has the same inclination as the capacitance load line **33a** of the first bit line **BL1**.

Likewise, at this timing, the transistors **T6** and **T8** are turned on and the source voltage **Vcc** as a voltage of "H" level is applied to the second reference cell plate line **RCP2**. Then, the ground voltage **Vss** is applied to the first electrodes of the ferroelectric capacitors **C6** and **C8** and the source voltage **Vcc** is applied to the second electrodes of the ferroelectric capacitors **C6** and **C8**. Each of the ferroelectric capacitors **C1**, **C3**, **C6** and **C8** then changes in the condition from the state in which no voltage is applied to the state in which a negative voltage ($-V_{cc}$) is applied thereto. Therefore, in the second reference cell **16**, the polarization charge of the ferroelectric capacitor **C6** moves from the point **C** to a point **I**, and in the fourth reference cell **18**, the polarization charge of the ferroelectric capacitor **C8** moves from the point **D** to a point **J**. Herein, the point **I** is located at the intersection point of the curve **31** with a capacitance load line **34a** of the second bit line **BL2**. The capacitance load line **34a** has a greater inclination than the capacitance load lines **33a** and **33c** because the second and fourth bit lines **BL2** and **BL4** are equalized to increase the capacitance values thereof.

By a series of actions performed until the time **t2** in FIG. 2, a charge **Q3** is read out on the first bit line **BL1**, and the first bit line **BL1** has a potential of "1" data corresponding to the point **E**. Also, a charge **Q2** is read out on the second and fourth bit lines **BL2** and

BL4, and the second and fourth bit lines **BL2** and **BL4** have reference potentials corresponding to the points **I** and **J**. Further, a charge **Q1** is read out on the third bit line **BL3**, and the third bit line **BL3** has a potential of “0” data corresponding to the point **H**. As a result, a potential difference **V1** is created across the first and second bit lines **BL1** and **BL2**, and a potential difference **V2** is created across the third and fourth bit lines **BL3** and **BL4**.

Next, at the timing of the time **t3** in FIG. 2, the first cell plate line **CP1** and the second reference cell plate line **RCP2** are inactivated, so that in the first memory cell **11**, the third memory cell **13**, the second reference cell **16**, and the fourth reference cell **18**, the voltages applied to the ferroelectric capacitors thereof change from the negative voltage (-Vcc) to zero volts.

By this change, in the first memory cell **11**, the polarization charge of the ferroelectric capacitor **C1** moves from the point **E** to a point **K** along a curve **35**. The point **K** is located at the intersection point of the curve **35** with a capacitance load line **33b** of the first bit line **BL1** drawn from a point **L** to which the point **E** moves along the voltage axis in the positive direction by the voltage **Vcc**. In the third memory cell **13**, the polarization charge of the ferroelectric capacitor **C3** moves from the point **H** to the point **D** along the curve **32**.

Likewise, in the second reference cell **16**, the polarization charge of the ferroelectric capacitor **C6** moves from the point **I** to a point **M** along a curve **36**. The point **M** is located at the intersection point of the curve **36** with a capacitance load line **34b** of the second bit line **BL2** drawn from a point **N** to which the point **I** moves along the voltage axis in the positive direction by the voltage **Vcc**. In the fourth reference cell **18**, the polarization charge of the ferroelectric capacitor **C8** moves from the point **J** to a point **P** along the curve **32**.

At that time, a potential difference **V3** corresponding to the potential difference across the points **P** and **D** is created across the first and second bit lines **BL1** and **BL2**, and

a potential difference **V4** corresponding to the potential difference across the points **P** and **N** is created across the third and fourth bit lines **BL3** and **BL4**.

Next, at the timing of the time **t4** in FIG. 2, the potential difference **V4** is amplified by the first sense amplifier **26**, whereby the first bit line **BL1** has the source voltage **Vcc** and the second bit line **BL2** has the ground voltage **Vss**. Thus, the first electrode of the ferroelectric capacitor **C1** of the first memory cell **11** has the source voltage **Vcc** applied. Therefore, the polarization charge of the ferroelectric capacitor **C1** moves from the point **K** to the point **A** along the curve **35**. The ferroelectric capacitor **C6** of the second reference cell **16** is separated from the second bit line **BL2**, so that the polarization charge thereof does not move and remains at the point **M**.

Likewise, the potential difference **V3** is amplified by the second sense amplifier **28**, whereby the third bit line **BL3** has the ground voltage **Vss** and the fourth bit line **BL4** has the source voltage **Vcc**. Thus, the ferroelectric capacitor **C3** of the third memory cell **13** keeps a voltage of zero volts, and the polarization charge thereof does not move and remains at the point **D**. The ferroelectric capacitor **C8** of the fourth reference cell **18** is separated from the fourth bit line **BL4**, so that the polarization charge thereof does not move and remains at the point **P**.

Subsequently, the reset data signal **RPD** and the second reset control signal **RPG2** are successively activated, whereby the source voltage **Vcc** derived from the reset data signal **RPD** is applied to the first electrode of the ferroelectric capacitor **C6** of the second reference cell **16**. The voltage applied to the ferroelectric capacitor **C6** is then changed from zero volts to a positive voltage. Therefore, the polarization charge of the ferroelectric capacitor **C6** moves from the point **M** to the point **A** along the curve **35**. In the ferroelectric capacitor **C8** of the fourth reference cell **18**, the ground voltage **Vss** is applied to the first electrode thereof. As a result, the ferroelectric capacitor **C8** keeps a voltage of zero volts and the polarization charge thereof does not move and remains at the point **P**.

Next, the second reference cell plate line **RCP2** is activated subsequently to the timing of the time **t5** in FIG. 2, whereby the source voltage **Vcc** is applied to the second electrodes of the ferroelectric capacitors **C6** and **C8** of the second and fourth reference cells **16** and **18**. The voltage applied to the ferroelectric capacitor **C6** is then changed from a positive voltage to zero volts and the polarization charge thereof moves from the point **A** to the point **C** along the curve **31**. On the other hand, the voltage applied to the ferroelectric capacitor **C8** is then changed from zero volts to a negative voltage and the polarization charge thereof moves from the point **P** to the point **B** along a curve **37**.

Thereafter, the reset data signal **RPD** and the second reset control signal **RPG2** are successively inactivated, so that the voltages of the first electrodes of the ferroelectric capacitors **C6** and **C8** become zero volts. Also, the second reference cell plate line **RCP2** is inactivated, so that the voltages of the second electrodes of the ferroelectric capacitors **C6** and **C8** become zero volts. From these actions, the ferroelectric capacitor **C6** of the second reference cell **16** keeps a voltage of zero volts and the polarization charge thereof remains at the point **C**. In the fourth reference cell **18**, the voltage applied to the ferroelectric capacitor **C8** is then changed from a negative voltage to zero volts and the polarization charge thereof moves from the point **B** to the point **D** along the curve **32**.

The bit line precharge signal **BP** is activated and the first word line **WL1** is inactivated. Then, in the ferroelectric capacitor **C1** of the first memory cell **11**, the voltage supply from the first bit line **BL1** to the first electrode thereof is stopped, so that the voltage applied to the ferroelectric capacitor **C1** becomes zero volts. Therefore, the polarization charge thereof moves from the point **A** to the point **C** along the curve **31**. At that time, the ferroelectric capacitor **C3** of the third memory cell **13** keeps a voltage of zero volts, so that the polarization charge thereof does not move and remains at the point **C**.

As is apparent from the above, the read operation of the memory cells is accomplished so that in the first memory cell **11** retaining "1" data, the polarization charge of the ferroelectric capacitor **C1** moves progressively in the order of the point **C**, the point

E, the point K, the point A, and the point C, and that in the third memory cell 13 retaining "0" data, the polarization charge of the ferroelectric capacitor C3 moves progressively in the order of the point D, the point H, the point B, and the point D. The read operation of the reference cells is accomplished so that in the second reference cell 16 retaining "1" data, the polarization charge of the ferroelectric capacitor C6 moves progressively in the order of the point C, the point I, the point M, the point A, and the point C, and that in the fourth reference cell 18 retaining "0" data, the polarization charge of the ferroelectric capacitor C8 moves progressively in the order of the point D, the point J, the point P, the point B, and the point D.

10 In the read operation of the reference cells described above, the amount of charge for polarization reversal in the ferroelectric capacitors C6 and C8 retaining "0" data is equal to the charge amount QSW1 between the point C and the point I shown in FIG. 3, which is smaller than that of the ferroelectric capacitor of the conventional ferroelectric memory device.

15 This description has been made of the case where "1" data is retained in the first memory cell 11 and "0" data is retained in the third memory cell 13. If different data are retained in the memory cells, the polarization charges of the ferroelectric capacitors C1 to C4 thereof move according to the data retained in the respective memory cells.

This description has been made of the case where the first and third memory cells 20 11 and 13 are read out. If the second and fourth memory cells 12 and 14 are read out, a reference potential is generated by utilizing the first and third reference cells. In this case, the polarization charges of the respective ferroelectric capacitors C2, C4, C5 and C7 move according to the data retained in the respective cells.

In the read operation described above, the second switch control signal REQ2 is 25 inactivated before the second reference word line RWL2 is activated, whereby noises caused in the inactivation of the second switch control signal REQ2 are not transferred to the ferroelectric capacitors C6 and C8. This prevents the polarization charges of the

ferroelectric capacitors from moving due to the noises accompanied with the inactivation of the second switch control signal **REQ2**. In particular, when the capacitances of the bit lines are large, the noises accompanied with the inactivation of the second switch control signal **REQ2** have a little effect on the potentials of the bit lines. This enables a reliable
5 read operation in the ferroelectric memory device.

As described above, the ferroelectric memory device of the first embodiment makes the amount of charge for polarization reversal of the ferroelectric capacitors **C5** to **C8** smaller, which reduces stresses placed on the ferroelectric capacitors **C5** to **C8** during the read operation. Accordingly, the characteristics of the number of rewriting operations can
10 be enhanced in the ferroelectric memory device.

(Modification of First Embodiment)

Hereinafter, a ferroelectric memory device according to an exemplary modification of the first embodiment will be described with reference to the drawings.

15 The ferroelectric memory device of this modification has a circuit configuration identical to that of the first embodiment shown in FIG. 1, but these devices differ in the read operation control by the control circuit 29. The following description is about the read operation of this modification, considering the difference in the read operation between this modification and the first embodiment.

20 FIG. 4 shows timings of the read operation in the ferroelectric memory device according to the modification of the first embodiment. As shown in FIG. 4, a series of actions performed from the initial state to the inactivation of the bit line precharge signal **BP** at time **t1** is the same as that of the read operation of the first embodiment performed until the time **t1**, which is shown in FIG. 2.

25 Then, prior to the timing of time **t2**, the second switch control signal **REQ2** is activated. Thus, the second switch circuit 24 is driven and the second and fourth bit lines **BL2** and **BL4** are equalized.

At the timing of the time **t2**, the first word line **WL1**, the first cell plate line **CP1**, the second reference word line **RWL2**, and the second reference cell plate line **RCP2** are activated.

In response, the transistors **T1** and **T3** are turned on and a voltage of “H” level is applied to the second electrodes of the ferroelectric capacitors **C1** and **C3**. Then, data retained in the first memory cell **11** is supplied to the first bit line **BL1** and data retained in the third memory cell **13** is supplied to the third bit line **BL3**.

In addition, the transistors **T6** and **T8** are turned on and a voltage of “H” level is applied to the second electrodes of the ferroelectric capacitors **C6** and **C8**. Then, “1” data retained in the second reference cell **16** is supplied to the second bit line **BL2** and “0” data retained in the fourth reference cell **18** is supplied to the fourth bit line **BL4**.

At this timing, the second and fourth bit lines **BL2** and **BL4** have already been equalized, so that the period of time until the potentials of the second and fourth bit lines **BL2** and **BL4** become a reference potential can be reduced.

As shown in FIG. 4, the first word line **WL1** and the second reference word line **RWL2** are activated subsequently to the activation of the second switch control signal **REQ2** and prior to the time **t2**. Alternatively, these two lines may be activated either concurrently with the first cell plate line **CP1** and the second reference cell plate line **RCP2**, or concurrently with the second switch control signal **REQ2**.

Thereafter, the first cell plate line **CP1** and the second reference cell plate line **RCP2** are inactivated at the timing of time **t3**. All the actions that follow are identical to the actions in the read operation of the first embodiment performed at the time **t3** and afterward, which are shown in FIG. 2, and omitted from this description.

Changes in charges in the ferroelectric accompanied with the read operation described above are the same as those in the first embodiment. Accordingly, the amount of charge for polarization reversal in the read operation of the reference cell is smaller than that of a conventional ferroelectric memory device.

The ferroelectric memory device according to this modification attains the same effects as the ferroelectric memory device of the first embodiment. Moreover, in order to keep the first cell plate line **CP1** and the second reference cell plate line **RCP2** activated for a predetermined period of time after the second switch control signal **REQ2** is activated, the first cell plate line **CP1** and the second reference cell plate line **RCP2** are activated with the equalization time secured by the activation of the second switch control signal **REQ2**. This contributes to the reduction of the time until the potentials of the second and fourth bit lines **BL2** and **BL4** become a reference potential. As a result, the ferroelectric memory device can attain a faster read operation.

(Second Embodiment)

Hereinafter, a ferroelectric memory device according to a second embodiment will be described with reference to the drawings.

The ferroelectric memory device of the second embodiment has a circuit configuration identical to that of the first embodiment shown in FIG. 1, but these devices differ in the read operation control by the control circuit 29. The following description is about the read operation of the second embodiment, considering the difference in the read operation between the second embodiment and the first embodiment.

FIG. 5 shows timings of the read operation in the ferroelectric memory device according to the second embodiment. As shown in FIG. 5, a series of actions performed from the initial state to the inactivation of the first cell plate line **CP1** and the second reference cell plate line **RCP2** at time **t3** is the same as that of the read operation of the first embodiment performed until the time **t3**, which is shown in FIG. 2.

Subsequently to these actions and prior to the timing of time **t4**, the second switch control signal **REQ2** and the second reference word line **RWL2** are successively inactivated. In response, the second switch circuit 24 is stopped to separate the second bit line **BL2** from the fourth bit line **BL4**, after which the transistors **T6** and **T8** are turned off

to separate the second and fourth reference cells **16** and **18** from the second and fourth bit lines **BL2** and **BL4**, respectively.

At that time, equalization is stopped with the capacitances of the ferroelectric capacitors **C6** and **C8** added to the second and fourth bit lines **BL2** and **BL4**. Therefore, when in particular the capacitances of the bit lines are small, noises accompanied with the inactivation of the second switch control signal **REQ2** are reduced.

Thereafter, the sense amplifier driving signal **SAE** is activated at the timing of time **t4**. All the actions that follow are identical to the actions in the read operation of the first embodiment performed at the time **t4** and afterward, which are shown in FIG. 2, and omitted from this description.

Changes (movement on FIG. 3) in the polarization charges of the ferroelectric capacitors accompanied with the read operation of the ferroelectric memory device of the second embodiment are identical to those of the first embodiment. To be more specific, the read operation of a memory cell is accomplished so that in a memory cell retaining "1" data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order of the point **C**, the point **E**, the point **K**, the point **A**, and the point **C**, and that in a memory cell retaining "0" data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order of the point **D**, the point **H**, the point **B**, and the point **D**. The read operation of a reference cell is accomplished so that in a reference cell retaining "1" data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order of the point **C**, the point **I**, the point **M**, the point **A**, and the point **C**, and that in a reference cell retaining "0" data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order of the point **D**, the point **J**, the point **P**, the point **B**, and the point **D**.

As described above, the ferroelectric memory device of the second embodiment makes the amount of charge for polarization reversal smaller as in the case of the first

embodiment, which enhances the characteristics of the number of rewriting operations in the ferroelectric memory device.

In the read operation of the second embodiment, moreover, the second switch control signal **REQ2** is inactivated, after which the second reference word line **RWL2** is inactivated. Therefore, when the capacitances of the bit lines are small, noises accompanied with the inactivation of the second switch control signal **REQ2** have a little effect on the bit lines. This enables a highly-reliable read operation in the ferroelectric memory device.

Also in the second embodiment, the second switch control signal **REQ2** is activated prior to the timing of the time **t2** as in the case of the modification of the first embodiment. Thus, a high speed operation of the ferroelectric memory device can be performed while the activation time of the second switch control signal **REQ2** coincides with the activation time of the first cell plate line **CP1** and the second reference cell plate line **RCP2**.

(Third Embodiment)

Hereinafter, a ferroelectric memory device according to a third embodiment will be described with reference to the drawings.

The ferroelectric memory device of the third embodiment has a circuit configuration identical to that of the first embodiment shown in FIG. 1, but these devices differ in the read operation control by the control circuit **29**. The following description is about the read operation of the third embodiment, considering the difference in the read operation between the third embodiment and the first embodiment.

FIG. 6 shows timings of the read operation in the ferroelectric memory device according to the third embodiment.

As shown in FIG. 6, a series of actions performed from the initial state to the activation of the first cell plate line **CP1** and the second reference cell plate line **RCP2** at

time **t2** is the same as that of the read operation of the first embodiment performed until the time **t2**, which is shown in FIG. 2. In response, a voltage of “H” level is applied to the second electrodes of the ferroelectric capacitors **C1** and **C3** and the second electrodes of the ferroelectric capacitors **C6** and **C8**. This initiates data output from the first memory cell **11**, the third memory cell **13**, the second reference cell **16**, and the fourth reference cell **18** to the respective bit lines.

Subsequently to this action and prior to the timing of time **t3**, the second reference word line **RWL2** and the second switch control signal **REQ2** are successively inactivated. In response, the second switch circuit **24** is stopped to separate the second bit line **BL2** from the fourth bit line **BL4**, after which the transistors **T6** and **T8** are turned off to separate the second and fourth reference cells **16** and **18** from the second and fourth bit lines **BL2** and **BL4**, respectively.

Then, at the timing of time **t3**, the sense amplifier driving signal **SAE** is activated to drive the first and second sense amplifiers **26** and **28**. In response, a potential difference across the first and second bit lines **BL1** and **BL2** is amplified so that the voltage value of the first bit line **BL1** is equal to the source voltage **Vcc** and the voltage value of the second bit line **BL2** is equal to the ground voltage **Vss**. Simultaneously, a potential difference across the third and fourth bit lines **BL3** and **BL4** is amplified so that the voltage value of the third bit line **BL3** is equal to the ground voltage **Vss** and the voltage value of the fourth bit line **BL4** is equal to the source voltage **Vcc**.

Next, at the timing of time **t4**, the first cell plate line **CP1** and the second reference cell plate line **RCP2** are inactivated. This stops voltage supply to the second electrodes of the ferroelectric capacitors **C1** and **C3** and the second electrodes of the ferroelectric capacitors **C6** and **C8**, which stops data output from the first and third memory cells **11** and **13** and the second and fourth reference cells **16** and **18** to the respective bit lines.

Next, the sense amplifier driving signal **SAE** is inactivated at the timing of time **t5**. Thereafter, the bit line precharge signal **BP** is activated and the first word line **WL1** is

inactivated, whereby the read operation of the first and third memory cells **11** and **13** is completed.

In this case, in the first and third memory cells **11** and **13**, the transistors **T1** and **T3** are on during the drive of the first and second sense amplifiers **26** and **28**. Therefore, “1” data and “0” data are rewritten in the first and third memory cells **11** and **13** in correspondence with the potentials of the first and third bit lines **BL1** and **BL3**, respectively.

In the second and fourth reference cells **16** and **18**, the second reference word line **RWL2** is inactivated, and then the reset data signal **RPD** is activated to have a voltage of “H” level. Thereafter, the second reference cell plate line **RCP2** is inactivated, and then the second reset control signal **RPG2** is activated. Thus, the second reset circuit **22** is driven to rewrite “1” data in the second reference cell **16**, and the fourth reset circuit **24** is driven to rewrite “0” data in the fourth reference cell **18**.

Next description using FIG. 3 will be made of changes (movement on FIG. 3) in polarization charges of the ferroelectric capacitors accompanied with the read operation in the ferroelectric memory device of the third embodiment. Note that “L” level in FIG. 6 is set at the ground potential value V_{ss} (0 V) and “H” level in FIG. 6 is set at the source voltage value V_{cc} (> 0 V).

First, at the timing of the time **t1** in FIG. 6, no voltage is applied to the ferroelectric capacitors **C1** to **C8** of the memory cells and the reference cells. Therefore, in the first memory cell **11** and the second reference cell **16** both of which retain “1” data, the polarization charges of the ferroelectric capacitors **C1** and **C6** are located at the point **C** in FIG. 3. In the third memory cell **13** and the fourth reference cell **18** both of which retain “0” data, the polarization charges of the ferroelectric capacitors **C3** and **C8** are located at the point **D** in FIG. 3.

Subsequently, at the timing of the time **t2** in FIG. 6, the transistors **T1** and **T3** are turned on and the source voltage V_{cc} as a voltage of “H” level is applied to the first cell

plate line **CP1**. Then, the ground voltage **Vss** is applied to the first electrodes of the ferroelectric capacitors **C1** and **C3** and the source voltage **Vcc** is applied to the second electrodes of the ferroelectric capacitors **C1** and **C3**. Likewise, the transistors **T6** and **T8** are turned on and the source voltage **Vcc** as a voltage of “H” level is applied to the second reference cell plate line **RCP2**. Then, the ground voltage **Vss** is applied to the first electrodes of the ferroelectric capacitors **C6** and **C8** and the source voltage **Vcc** is applied to the second electrodes of the ferroelectric capacitors **C6** and **C8**. Each of the ferroelectric capacitors **C1**, **C3**, **C6** and **C8** then changes in the condition from the state in which no voltage is applied to the state in which a negative voltage ($-V_{cc}$) is applied thereto.

At this timing, in the first memory cell **11**, the polarization charge of the ferroelectric capacitor **C1** moves from the point **C** to the point **E** along the curve **31**. In the third memory cell **13**, the polarization charge of the ferroelectric capacitor **C3** moves from the point **D** to the point **H** along the curve **32**. Likewise, in the second reference cell **16**, the polarization charge of the ferroelectric capacitor **C6** moves from the point **C** to the point **I**, and in the fourth reference cell **18**, the polarization charge of the ferroelectric capacitor **C8** moves from the point **D** to the point **J**.

At that time, a charge **Q3** is read out on the first bit line **BL1**, and the first bit line **BL1** has a potential of “1” data corresponding to the point **E**. Also, a charge **Q2** is read out on the second and fourth bit lines **BL2** and **BL4**, and the second and fourth bit lines **BL2** and **BL4** have reference potentials corresponding to the points **I** and **J**. Further, a charge **Q1** is read out on the third bit line **BL3**, and the third bit line **BL3** has a potential of “0” data corresponding to the point **H**. As a result, a potential difference **V1** is created across the first and second bit lines **BL1** and **BL2**, and a potential difference **V2** is created across the third and fourth bit lines **BL3** and **BL4**.

Next, at the timing of the time **t3** in FIG. 6, the potential difference **V2** is amplified by the first sense amplifier **26**, whereby the first bit line **BL1** has the source voltage **Vcc**

and the second bit line **BL2** has the ground voltage **Vss**. Thus, the first electrode of the ferroelectric capacitor **C1** of the first memory cell **11** has the source voltage **Vcc** applied by the first bit line **BL1**, and the second electrode thereof has the source voltage **Vcc** applied by the first cell plate line **CP1**. Therefore, the polarization charge of the ferroelectric capacitor **C1** moves from the point **E** to the point **K** along the curve **35**. The ferroelectric capacitor **C6** of the second reference cell **16** is separated from the second bit line **BL2**, so that the polarization charge thereof does not move and remains at the point **I**.

Likewise, the potential difference **V1** is amplified by the second sense amplifier **28**, whereby the third bit line **BL3** has the ground voltage **Vss** and the fourth bit line **BL4** has the source voltage **Vcc**. Thus, the ferroelectric capacitor **C3** of the third memory cell **13** keeps a negative voltage (**-Vcc**) applied, and the polarization charge thereof does not move and remains at the point **H**. The ferroelectric capacitor **C8** of the fourth reference cell **18** is separated from the fourth bit line **BL4**, so that the polarization charge thereof does not move and remains at the point **J**.

Next, at the timing of the time **t4** in FIG. 6, the first cell plate line **CP1** and the second reference cell plate line **RCP2** are inactivated, so that in the first memory cell **11**, the third memory cell **13**, the second reference cell **16**, and the fourth reference cell **18**, the voltages applied to the ferroelectric capacitors **C1**, **C3**, **C6** and **C8** thereof change to voltages in the positive direction.

By this change, in the first memory cell **11**, the polarization charge of the ferroelectric capacitor **C1** moves from the point **K** to the point **A** along the curve **35**. In the third memory cell **13**, the polarization charge of the ferroelectric capacitor **C3** moves from the point **H** to the point **D** along the curve **32**.

Likewise, in the second reference cell **16**, the polarization charge of the ferroelectric capacitor **C6** moves from the point **I** to the point **M** along the curve **36**. In the fourth reference cell **18**, the polarization charge of the ferroelectric capacitor **C8** moves from the point **J** to the point **D** along the curve **32**.

Subsequently, the sense amplifier driving signal **SAE** is inactivated and then the first word line **WL1** is inactivated, whereby the first electrodes of the ferroelectric capacitors **C1** and **C3** in the first and third memory cells **11** and **13** each have a voltage of zero volts. Thus, the voltage of the ferroelectric capacitor **C1** is changed to zero volts so that the polarization charge thereof moves from the point **A** to the point **C** along the curve **31**. On the other hand, the ferroelectric capacitor **C3** keeps a voltage of zero volts and the polarization charge thereof does not move and remains at the point **D**.

Furthermore, the second reference cell plate line **RCP2** is inactivated and then the second reset control signal **RPG2** is activated. Thus, the source voltage **Vcc** as the reset data signal **RPD** is applied to the first electrode of the ferroelectric capacitor **C6** of the second reference cell **16**, while the ground voltage **Vss** is applied to the first electrode of the ferroelectric capacitor **C8** of the fourth reference cell **18**. As a result, the ferroelectric capacitor **C6** is changed to a state that a positive voltage is applied, so that the polarization charge thereof moves from the point **M** to the point **A** along the curve **35**. On the other hand, the ferroelectric capacitor **C8** keeps a voltage of zero volts, so that the polarization charge thereof does not move and remains at the point **D**.

Thereafter, the reset data signal **RPD** and the second reset control signal **RPG2** are successively inactivated subsequently to the timing of the time **t5** in FIG. 6, so that the voltages of the first electrodes of the ferroelectric capacitors **C6** and **C8** become zero volts.

From these actions, in the second reference cell **16**, the voltage applied to the ferroelectric capacitor **C6** is then changed from a positive voltage to zero volts and the polarization charge thereof moves from the point **A** to the point **C** along the curve **31**. In the fourth reference cell **18**, the ferroelectric capacitor **C8** thereof keeps a voltage of zero volts, so that the polarization charge thereof does not move and remains at the point **D**.

The movement on FIG. 3 of the polarization charges in the ferroelectric capacitors accompanied with the read operation of the ferroelectric memory device of the third embodiment is as follows. In a memory cell retaining "1" data, the polarization charge of

the ferroelectric capacitor thereof moves progressively in the order of the point **C**, the point **E**, the point **K**, the point **A**, and the point **C**, and in a memory cell retaining “0” data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order of the point **D**, the point **H**, the point **B**, and the point **D**. Regarding reference cells, in a reference cell retaining “1” data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order of the point **C**, the point **I**, the point **M**, the point **A**, and the point **C**, and in a reference cell retaining “0” data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order of the point **D**, the point **J**, and the point **D**.

10 As described above, the ferroelectric memory device of the third embodiment makes the amount of charge for polarization reversal smaller as in the case of the first embodiment, which enhances the characteristics of the number of rewriting operations in the ferroelectric memory device.

Moreover, the cell plate line and the reference plate line are activated even during the drive of the sense amplifier, which raises the potential of the bit line in the inactivation of the switch control signal. This reduces the effect of noises accompanied with the inactivation of the switch control signal, which enables a highly-reliable read operation in the ferroelectric memory device.

Also in the third embodiment, the second switch control signal **REQ2** is activated prior to the timing of the time **t2** as in the case of the modification of the first embodiment. Thus, a high speed operation of the ferroelectric memory device can be performed while the activation time of the second switch control signal **REQ2** coincides with the activation time of the first cell plate line **CP1** and the second reference cell plate line **RCP2**.

25 (Fourth Embodiment)

Hereinafter, a ferroelectric memory device according to a fourth embodiment will be described with reference to the drawings.

The ferroelectric memory device of the fourth embodiment has a circuit configuration identical to that of the first embodiment shown in FIG. 1, but these devices differ in the read operation control by the control circuit 29. The following description is about the read operation of the fourth embodiment, considering the difference in the read operation between the fourth embodiment and the first embodiment.

FIG. 7 shows timings of the read operation in the ferroelectric memory device according to the fourth embodiment.

As shown in FIG. 7, a series of actions performed from the initial state to the activation of the first cell plate line CP1 and the second reference cell plate line RCP2 at time t2 is the same as that of the read operation of the first embodiment performed until the time t2, which is shown in FIG. 2. In response, a voltage of "H" level is applied to the second electrodes of the ferroelectric capacitors C1 and C3 and the second electrodes of the ferroelectric capacitors C6 and C8. This initiates data output from the first memory cell 11, the third memory cell 13, the second reference cell 16, and the fourth reference cell 18 to the respective bit lines.

Subsequently to this action and prior to the timing of time t3, the second switch control signal REQ2 and the second reference word line RWL2 are successively inactivated. In response, the second switch circuit 24 is stopped to separate the second bit line BL2 from the fourth bit line BL4, after which the transistors T6 and T8 are turned off to separate the second and fourth reference cells 16 and 18 from the second and fourth bit lines BL2 and BL4, respectively.

Then, at the timing of time t3, the sense amplifier driving signal SAE is activated to drive the first and second sense amplifiers 26 and 28. In response, a potential difference across the first and second bit lines BL1 and BL2 is amplified so that the voltage value of the first bit line BL1 is equal to the source voltage Vcc and the voltage value of the second bit line BL2 is equal to the ground voltage Vss. Simultaneously, a potential difference across the third and fourth bit lines BL3 and BL4 is amplified so that the voltage value of

the third bit line **BL3** is equal to the ground voltage **Vss** and the voltage value of the fourth bit line **BL4** is equal to the source voltage **Vcc**.

Next, at the timing of time **t4**, the first cell plate line **CP1** and the second reference cell plate line **RCP2** are inactivated. This stops voltage supply to the second electrodes of the ferroelectric capacitors **C1** and **C3** and the second electrodes of the ferroelectric capacitors **C6** and **C8**, which stops data output from the first and third memory cells **11** and **13** and the second and fourth reference cells **16** and **18** to the respective bit lines.

Thereafter, the sense amplifier driving signal **SAE** is inactivated at the timing of time **t5**. All the actions that follow are identical to the actions in the read operation of the third embodiment performed at the time **t5** and afterward, which are shown in FIG. 6, and omitted from this description.

Next description using FIG. 3 will be made of changes (movement on FIG. 3) in polarization charges of the ferroelectric capacitors accompanied with the read operation in the ferroelectric memory device of the fourth embodiment. Note that “L” level in FIG. 7 is set at the ground potential value **Vss** (0 V) and “H” level in FIG. 7 is set at the source voltage value **Vcc** (> 0 V).

First, at the timing of the time **t1** in FIG. 7, no voltage is applied to the ferroelectric capacitors **C1** to **C8** of the memory cells and the reference cells. Therefore, in the first memory cell **11** and the second reference cell **16** both of which retain “1” data, the polarization charges of the ferroelectric capacitors **C1** and **C6** are located at the point **C** in FIG. 3. In the third memory cell **13** and the fourth reference cell **18** both of which retain “0” data, the polarization charges of the ferroelectric capacitors **C3** and **C8** are located at the point **D** in FIG. 3.

At the timing of the time **t2** in FIG. 7, the transistors **T1** and **T3** are turned on and the source voltage **Vcc** as a voltage of “H” level is applied to the first cell plate line **CP1**. Then, the ground voltage **Vss** is applied to the first electrodes of the ferroelectric capacitors **C1** and **C3** and the source voltage **Vcc** is applied to the second electrodes of the

ferroelectric capacitors **C1** and **C3**. Likewise, the transistors **T6** and **T8** are turned on and the source voltage **Vcc** as a voltage of “H” level is applied to the second reference cell plate line **RCP2**. Then, the ground voltage **Vss** is applied to the first electrodes of the ferroelectric capacitors **C6** and **C8** and the source voltage **Vcc** is applied to the second electrodes of the ferroelectric capacitors **C6** and **C8**. Each of the ferroelectric capacitors **C1**, **C3**, **C6** and **C8** then changes in the condition from the state in which no voltage is applied to the state in which a negative voltage ($-V_{cc}$) is applied thereto.

At this timing, in the first memory cell **11**, the polarization charge of the ferroelectric capacitor **C1** moves from the point **C** to the point **E** along the curve **31**. In the third memory cell **13**, the polarization charge of the ferroelectric capacitor **C3** moves from the point **D** to the point **H** along the curve **32**. Likewise, in the second reference cell **16**, the polarization charge of the ferroelectric capacitor **C6** moves from the point **C** to the point **I**, and in the fourth reference cell **18**, the polarization charge of the ferroelectric capacitor **C8** moves from the point **D** to the point **J**.

At that time, a charge **Q3** is read out on the first bit line **BL1**, and the first bit line **BL1** has a potential of “1” data corresponding to the point **E**. Also, a charge **Q2** is read out on the second and fourth bit lines **BL2** and **BL4**, and the second and fourth bit lines **BL2** and **BL4** have reference potentials corresponding to the points **I** and **J**. Further, a charge **Q1** is read out on the third bit line **BL3**, and the third bit line **BL3** has a potential of “0” data corresponding to the point **H**. As a result, a potential difference **V1** is created across the first and second bit lines **BL1** and **BL2**, and a potential difference **V2** is created across the third and fourth bit lines **BL3** and **BL4**.

Next, at the timing of the time **t3** in FIG. 7, the potential difference **V2** is amplified by the first sense amplifier **26**, whereby the first bit line **BL1** has the source voltage **Vcc** and the second bit line **BL2** has the ground voltage **Vss**. Thus, the first electrode of the ferroelectric capacitor **C1** of the first memory cell **11** has the source voltage **Vcc** applied by the first bit line **BL1**, and the second electrode thereof has the source voltage **Vcc**

applied by the first cell plate line **CP1**. Therefore, the polarization charge of the ferroelectric capacitor **C1** moves from the point **E** to the point **K** along the curve **35**. The ferroelectric capacitor **C6** of the second reference cell **16** is separated from the second bit line **BL2**, so that the polarization charge thereof does not move and remains at the point **I**.

5 Likewise, the potential difference **V1** is amplified by the second sense amplifier **28**, whereby the third bit line **BL3** has the ground voltage **Vss** and the fourth bit line **BL4** has the source voltage **Vcc**. Thus, the ferroelectric capacitor **C3** of the third memory cell **13** keeps a negative voltage (**-Vcc**) applied, so that the polarization charge thereof does not move and remains at the point **H**. The ferroelectric capacitor **C8** of the fourth reference
10 cell **18** is separated from the fourth bit line **BL4**, so that the polarization charge thereof does not move and remains at the point **J**.

Next, at the timing of the time **t4** in FIG. 7, the first cell plate line **CP1** and the second reference cell plate line **RCP2** are inactivated, so that in the first memory cell **11**, the third memory cell **13**, the second reference cell **16**, and the fourth reference cell **18**, the
15 voltages applied to the ferroelectric capacitors **C1**, **C3**, **C6** and **C8** thereof change to voltages in the positive direction.

By this change, in the first memory cell **11**, the polarization charge of the ferroelectric capacitor **C1** moves from the point **K** to the point **A** along the curve **35**. In the third memory cell **13**, the polarization charge of the ferroelectric capacitor **C3** moves
20 from the point **H** to the point **D** along the curve **32**.

Likewise, in the second reference cell **16**, the polarization charge of the ferroelectric capacitor **C6** moves from the point **I** to the point **M** along the curve **36**. In the fourth reference cell **18**, the polarization charge of the ferroelectric capacitor **C8** moves from the point **J** to the point **D** along the curve **32**.

25 Subsequently, the sense amplifier driving signal **SAE** is inactivated and then the first word line **WL1** is inactivated, whereby the first electrodes of the ferroelectric capacitors **C1** and **C3** in the first and third memory cells **11** and **13** each have a voltage of

zero volts. Thus, the voltage of the ferroelectric capacitor **C1** is changed to zero volts so that the polarization charge thereof moves from the point **A** to the point **C** along the curve **31**. On the other hand, the ferroelectric capacitor **C3** keeps a voltage of zero volts and the polarization charge thereof does not move and remains at the point **D**.

5 Furthermore, the second reference cell plate line **RCP2** is inactivated and then the second reset control signal **RPG2** is activated. Thus, the source voltage **Vcc** as the reset data signal **RPD** is applied to the first electrode of the ferroelectric capacitor **C6** of the second reference cell **16**, while the ground voltage **Vss** is applied to the first electrode of the ferroelectric capacitor **C8** of the fourth reference cell **18**. As a result, the ferroelectric
10 capacitor **C6** is changed to a state that a positive voltage is applied, so that the polarization charge thereof moves from the point **M** to the point **A** along the curve **35**. On the other hand, the ferroelectric capacitor **C8** keeps a voltage of zero volts, so that the polarization charge thereof does not move and remains at the point **D**.

Thereafter, the reset data signal **RPD** and the second reset control signal **RPG2** are
15 successively inactivated subsequently to the timing of the time **t5** in FIG. 7, so that the voltages of the first electrodes of the ferroelectric capacitors **C6** and **C8** become zero volts. From these actions, in the second reference cell **16**, the voltage applied to the ferroelectric capacitor **C6** is then changed from a positive voltage to zero volts and the polarization charge thereof moves from the point **A** to the point **C** along the curve **31**. In the fourth
20 reference cell **18**, the ferroelectric capacitor **C8** thereof keeps a voltage of zero volts, so that the polarization charge thereof does not move and remains at the point **D**.

The movement on FIG. 3 of the polarization charges in the ferroelectric capacitors accompanied with the read operation of the ferroelectric memory device of the fourth embodiment is as follows. In a memory cell retaining "1" data, the polarization charge of
25 the ferroelectric capacitor thereof moves progressively in the order of the point **C**, the point **E**, the point **K**, the point **A**, and the point **C**, and in a memory cell retaining "0" data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order

of the point **D**, the point **H**, the point **B**, and the point **D**. Regarding reference cells, in a reference cell retaining “1” data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order of the point **C**, the point **I**, the point **M**, the point **A**, and the point **C**, and in a reference cell retaining “0” data, the polarization charge of the ferroelectric capacitor thereof moves progressively in the order of the point **D**, the point **J**, and the point **D**.

As described above, the ferroelectric memory device of the fourth embodiment makes the amount of charge for polarization reversal smaller as in the case of the first embodiment, which enhances the characteristics of the number of rewriting operations in the ferroelectric memory device.

In the read operation of the fourth embodiment, moreover, the cell plate line and the reference plate line are activated even during the drive of the sense amplifier, which raises the potential of the bit line in the inactivation of the switch control signal. This reduces the effect of noises accompanied with the inactivation of the switch control signal, which enables a highly-reliable read operation in the ferroelectric memory device.

Also in the fourth embodiment, the second switch control signal **REQ2** is activated prior to the timing of the time **t2** as in the case of the modification of the first embodiment. Thus, a high speed operation of the ferroelectric memory device can be performed while the activation time of the second switch control signal **REQ2** coincides with the activation time of the first cell plate line **CP1** and the second reference cell plate line **RCP2**.

(Fifth Embodiment)

Hereinafter, a ferroelectric memory device according to a fifth embodiment will be described with reference to the drawings.

The ferroelectric memory device of the fifth embodiment has a circuit configuration identical to that of the first embodiment shown in FIG. 1, but these devices differ in the read operation control by the control circuit **29**. The following description is

about the read operation of the fifth embodiment, considering the difference in the read operation between the fifth embodiment and the first embodiment.

FIG. 8 shows timings of the read operation in the ferroelectric memory device according to the fifth embodiment.

5 As shown in FIG. 8, a series of actions performed from the initial state to the inactivation of the bit line precharge signal **BP** at time **t1** is the same as that of the read operation of the first embodiment performed until the time **t1**, which is shown in FIG. 2.

Subsequently, at the timing of the time **t2**, the first word line **WL1**, the first cell plate line **CP1**, the second reference word line **RWL2**, and the second reference cell plate
10 line **RCP2** are activated.

In response, the transistors **T1** and **T3** are turned on and a voltage of “H” level is applied to the second electrodes of the ferroelectric capacitors **C1** and **C3**. Then, data retained in the first memory cell **11** is supplied to the first bit line **BL1** and data retained in the third memory cell **13** is supplied to the third bit line **BL3**.

15 In addition, the transistors **T6** and **T8** are turned on and a voltage of “H” level is applied to the second electrodes of the ferroelectric capacitors **C6** and **C8**. Then, “1” data retained in the second reference cell **16** is supplied to the second bit line **BL2** and “0” data retained in the fourth reference cell **18** is supplied to the fourth bit line **BL4**.

Next, at the timing of time **t3**, the first cell plate line **CP1** and the second reference
20 cell plate line **RCP2** are inactivated. This stops voltage supply to the second electrodes of the ferroelectric capacitors **C1** and **C3** and the second electrodes of the ferroelectric capacitors **C6** and **C8**, which stops data output from the first and third memory cells **11** and **13** and the second and fourth reference cells **16** and **18** to the respective bit lines **BL1** to **BL4**.

25 Subsequently to this action and prior to the timing of time **t4**, the second switch control signal **REQ2** is kept activated for a predetermined period of time. In response, the second switch circuit **24** is driven to equalize the second and fourth bit lines **BL2** and **BL4**.

As a result, the second and fourth bit lines **BL2** and **BL4** have, as a reference potential, an intermediate potential between the potential corresponding to “1” data and the potential corresponding to “0” data.

Subsequently to this, the second reference word line **RWL2** is successively
5 inactivated. In response, the transistors **T6** and **T8** are turned off to separate the second and fourth reference cells **16** and **18** from the second and fourth bit lines **BL2** and **BL4**, respectively.

Then, at the timing of time **t4**, the sense amplifier driving signal **SAE** is activated to drive the first and second sense amplifiers **26** and **28**. In response, a potential difference
10 across the first and second bit lines **BL1** and **BL2** is amplified so that the voltage value of the first bit line **BL1** is equal to the source voltage **Vcc** and the voltage value of the second bit line **BL2** is equal to the ground voltage **Vss**. Simultaneously, a potential difference across the third and fourth bit lines **BL3** and **BL4** is amplified so that the voltage value of the third bit line **BL3** is equal to the ground voltage **Vss** and the voltage value of the fourth
15 bit line **BL4** is equal to the source voltage **Vcc**.

Next, the reset data signal **RPD** and the second reset control signal **RPG2** are successively activated, thereby performing rewriting in the second and fourth reference cells **16** and **18** by utilizing the second and fourth reset circuits **20** and **22**. In this rewriting, the first electrode of the ferroelectric capacitor **C6** of the second reference cell
20 **16** is supplied with the ground voltage **Vss**, so that “0” data is written in the second reference cell **16**. On the other hand, the first electrode of the ferroelectric capacitor **C8** of the fourth reference cell **18** is supplied with a voltage of “H” level serving as a reset data signal **RPD**, so that “1” data is written in the fourth reference cell **18**.

Thereafter, the bit line precharge signal **BP** is activated and in addition the first
25 word line **WL1**, the reset data signal **RPD**, and the second reset control signal **RPG2** are successively inactivated to restore the device condition to the initial state. The read operation of the device is thus completed.

Next description using FIG. 3 will be made of changes (movement on FIG. 3) in polarization charges of the ferroelectric capacitors accompanied with the read operation in the ferroelectric memory device of the fifth embodiment. Note that “L” level in FIG. 8 is set at the ground potential value V_{ss} (0 V) and “H” level in FIG. 8 is set at the source voltage value V_{cc} (> 0 V).

First, at the timing of the time t_1 in FIG. 8, no voltage is applied to the ferroelectric capacitors **C1** to **C8** of the memory cells and the reference cells. Therefore, in the first memory cell **11** and the second reference cell **16** both of which retain “1” data, the polarization charges of the ferroelectric capacitors **C1** and **C6** are located at the point **C** in FIG. 3. In the third memory cell **13** and the fourth reference cell **18** both of which retain “0” data, the polarization charges of the ferroelectric capacitors **C3** and **C8** are located at the point **D** in FIG. 3.

At the timing of the time t_2 in FIG. 8, the transistors **T1** and **T3** are turned on and the source voltage V_{cc} as a voltage of “H” level is applied to the first cell plate line **CP1**. Then, the ground voltage V_{ss} is applied to the first electrodes of the ferroelectric capacitors **C1** and **C3** and the source voltage V_{cc} is applied to the second electrodes of the ferroelectric capacitors **C1** and **C3**. Likewise, the transistors **T6** and **T8** are turned on and the source voltage V_{cc} as a voltage of “H” level is applied to the second reference cell plate line **RCP2**. Then, the ground voltage V_{ss} is applied to the first electrodes of the ferroelectric capacitors **C6** and **C8** and the source voltage V_{cc} is applied to the second electrodes of the ferroelectric capacitors **C6** and **C8**. Each of the ferroelectric capacitors **C1**, **C3**, **C6** and **C8** then changes in the condition from the state in which no voltage is applied to the state in which a negative voltage ($-V_{cc}$) is applied thereto.

By this change, in the first memory cell **11**, the polarization charge of the ferroelectric capacitor **C1** moves from the point **C** to the point **E** along the curve **31**. In the third memory cell **13**, the polarization charge of the ferroelectric capacitor **C3** moves from the point **D** to the point **H** along the curve **32**. At this timing, the second switch circuit **24**

is under suspension, so that the second and fourth bit lines **BL2** and **BL4** have the same bit line capacitance as the first bit line **BL1**. Thus, in the second reference cell **16** retaining “1” data, the polarization charge of the ferroelectric capacitor **C6** moves from the point **C** to the point **E**, and in the fourth reference cell **18**, the polarization charge of the ferroelectric capacitor **C8** moves from the point **D** to the point **H**.

At this timing, a charge **Q3** is read out on the first and second bit lines **BL1** and **BL2**, and the first and second bit lines **BL1** and **BL2** have a potential of “1” data corresponding to the point **E**. Also, a charge **Q1** is read out on the third and fourth bit lines **BL3** and **BL4**, and the third and fourth bit lines **BL3** and **BL4** have a potential of “0” data corresponding to the point **H**.

Next, at the timing of the time **t3** in FIG. 8, the first cell plate line **CP1** and the second reference cell plate line **RCP2** are inactivated, so that in the first memory cell **11**, the third memory cell **13**, the second reference cell **16**, and the fourth reference cell **18**, the voltages applied to the respective ferroelectric capacitors change from the negative voltage (**-Vcc**) to zero volts.

By this change, in the first memory cell **11**, the polarization charge of the ferroelectric capacitor **C1** moves from the point **E** to the point **K** along the curve **35**. In the third memory cell **13**, the polarization charge of the ferroelectric capacitor **C3** moves from the point **H** to the point **D** along the curve **32**.

Likewise, in the second reference cell **16**, the polarization charge of the ferroelectric capacitor **C6** moves from the point **E** to the point **K** along the curve **36**. In the fourth reference cell **18**, the polarization charge of the ferroelectric capacitor **C8** moves from the point **H** to the point **D** along the curve **32**.

The second switch control signal **REQ2** is activated prior to the timing of the time **t4** shown in FIG. 8. In response, the second switch circuit **24** is driven to equalize the second and fourth bit lines **BL2** and **BL4**. As a result, the second and fourth bit lines **BL2**

and **BL4** have an intermediate potential between the potential of “1” data corresponding to the point **E** and the potential of “0” data corresponding to the point **H**.

Next, at the timing of the time **t4** in FIG. 8, the potential difference is amplified by the first sense amplifier **26**, whereby the first bit line **BL1** has the source voltage **Vcc** and the second bit line **BL2** has the ground voltage **Vss**. Thus, the first electrode of the ferroelectric capacitor **C1** of the first memory cell **11** has the source voltage **Vcc** applied. Therefore, the polarization charge of the ferroelectric capacitor **C1** moves from the point **K** to the point **A** along the curve **35**. The ferroelectric capacitor **C6** of the second reference cell **16** is separated from the second bit line **BL2**, so that the polarization charge thereof does not move and remains at the point **K**.

Likewise, the potential difference is amplified by the second sense amplifier **28**, whereby the third bit line **BL3** has the ground voltage **Vss** and the fourth bit line **BL4** has the source voltage **Vcc**. Thus, the ferroelectric capacitor **C3** of the third memory cell **13** keeps a voltage of zero volts, and the polarization charge thereof does not move and remains at the point **D**. The ferroelectric capacitor **C8** of the fourth reference cell **18** is separated from the fourth bit line **BL4**, so that the polarization charge thereof does not move and remains at the point **D**.

The reset data signal **RPD** and the second reset control signal **RPG2** are then successively activated, whereby the source voltage **Vcc** derived from the reset data signal **RPD** is applied to the first electrode of the ferroelectric capacitor **C6** of the second reference cell **16**. In the fourth reference cell **18**, the ground voltage **Vss** is applied to the first electrode of the ferroelectric capacitor **C8** thereof. Therefore, the voltage applied to the ferroelectric capacitor **C6** is then changed from zero volts to a positive voltage, so that the polarization charge thereof moves from the point **K** to the point **A** along the curve **35**. On the other hand, the ferroelectric capacitor **C8** keeps a voltage of zero volts, so that the polarization charge thereof does not move and remains at the point **D**.

Thereafter, the reset data signal **RPD** and the second reset control signal **RPG2** are successively inactivated subsequently to the timing of the time **t5** in FIG. 8, so that the voltages of the first electrodes of the ferroelectric capacitors **C6** and **C8** become zero volts. Also, the second reference cell plate line **RCP2** is inactivated, so that the voltages of the second electrodes of the ferroelectric capacitors **C6** and **C8** become zero volts. From these actions, in the second reference cell **16**, the voltage applied to the ferroelectric capacitor **C6** is then changed from a positive voltage to zero volts and the polarization charge thereof moves from the point **A** to the point **C** along the curve **31**. In the fourth reference cell **18**, the ferroelectric capacitor **C8** thereof keeps a voltage of zero volts and the polarization charge thereof remains at the point **D**.

As is apparent from the above, in the read operation in the ferroelectric memory device of the fifth embodiment, the polarization charges of the ferroelectric capacitors of the memory cells and the reference cells move along the same path during the read operation. To be more specific, in a memory cell and a reference cell both of which retain “1” data, the polarization charges of the ferroelectric capacitors move progressively in the order of the point **C**, the point **E**, the point **K**, the point **A**, and the point **C**. In a memory cell and a reference cell both of which retain “0” data, the polarization charges of the ferroelectric capacitors move progressively in the order of the point **D**, the point **H**, the point **B**, and the point **D**. Accordingly, in the read operation of the ferroelectric memory device of the fifth embodiment, the amount of charge for polarization reversal is equal to the charge amount **QSW2** between the point **C** and the point **E** shown in FIG. 3, which is smaller than that of the first embodiment.

As described above, the ferroelectric memory device of the fifth embodiment makes the amount of charge for polarization reversal smaller than that of the first embodiment. As a result, the characteristics of the number of rewriting operations can be enhanced further in the ferroelectric memory device.

Moreover, since the reference cells supply “1” data and “0” data to the respective bit lines before the switch control signal is activated, the bit lines are equalized with the capacitances of the ferroelectric capacitors not added to the bit lines. As a result, a reference potential can be generated accurately in the ferroelectric memory device.